



INA818 35 μ V オフセット、8nV/ $\sqrt{\text{Hz}}$ ノイズ、低消費電力、高精度計装アンプ

1 特長

- 低いオフセット電圧: 10 μ V (標準値)、35 μ V (最大値)
- ゲイン・ドリフト係数: 5ppm/ $^{\circ}\text{C}$ ($G = 1$)、35ppm/ $^{\circ}\text{C}$ ($G > 1$) (最大値)
- ノイズ: 8nV/ $\sqrt{\text{Hz}}$
- 帯域幅: 2MHz ($G = 1$)、270kHz ($G = 100$)
- 1nF の容量性負荷で安定
- $\pm 60\text{V}$ まで入力を保護
- 同相除去比: 110dB、 $G = 10$ (最小値)
- 電源電圧除去比: 100dB、 $G = 1$ (最小値)
- 消費電流: 385 μ A (最大値)
- 電源電圧範囲
 - シングル電源: 4.5V $\sim$ 36V
 - デュアル電源: $\pm 2.25\text{V} \sim \pm 18\text{V}$
- 規定温度範囲: $-40^{\circ}\text{C} \sim +125^{\circ}\text{C}$
- パッケージ: 8 ピン SOIC

2 アプリケーション

- 産業用モニタ
- 流量トランスミッタ
- バッテリー・テスト機器
- マルチパラメータ患者モニタ
- アナログ入力モジュール
- 半導体試験機器
- ポータブル計測装置

3 概要

INA818 は、単一電源またはデュアル電源の非常に幅広い電圧範囲で動作する、低消費電力の高精度計装アンプです。1 個の外付け抵抗で、1 $\sim$ 10000 の任意のゲインを設定できます。このデバイスは、入力オフセット電圧、オフセット電圧ドリフト、入力バイアス電流、入力電圧ノイズ、入力電流ノイズを極めて低く抑えるスーパー β 入力トランジスタを使用することで、高い精度を実現します。追加回路により、 $\pm 60\text{V}$ までの過電圧から入力を保護します。

INA818 は、高い同相除去比を実現するよう最適化されています。 $G = 1$ での同相除去比は、全入力同相範囲を通じて 90dB を上回ります。このデバイスは、4.5V 単一電源および最高 $\pm 18\text{V}$ のデュアル電源による低電圧動作用に設計されています。

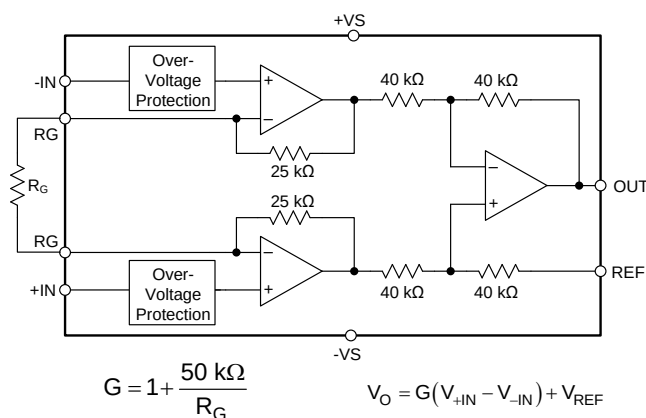
INA818 は 8 ピン SOIC パッケージで供給され、 $-40^{\circ}\text{C} \sim +125^{\circ}\text{C}$ の温度範囲で動作が規定されています。

製品情報⁽¹⁾

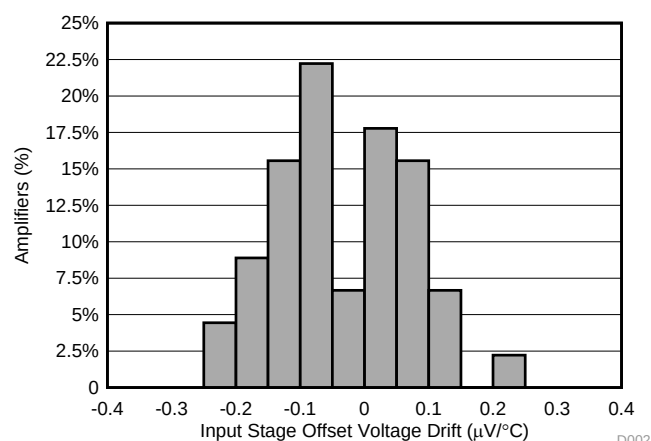
型番	パッケージ	本体サイズ(公称)
INA818	SOIC (8)	4.90mm $\times$ 3.91mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にあるパッケージ・オプションについての付録を参照してください。

INA818 の簡略化された内部回路図



入力段のオフセット電圧ドリフトの代表的な分布



D002



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4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

2019年4月発行のものから更新

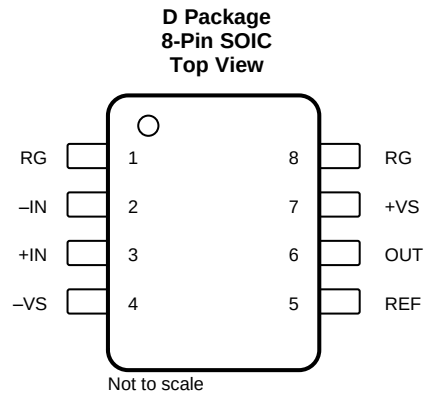
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•	ドキュメントのステータスを「事前情報」から「量産データ」に変更	1
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5 Device Comparison Table

DEVICE	DESCRIPTION	GAIN EQUATION	RG PINS AT PIN
INA818	35- μ V Offset, 0.4 μ V/ $^{\circ}$ C V_{OS} Drift, 8-nV/ $\sqrt{\text{Hz}}$ Noise, Low-Power, Precision Instrumentation Amplifier	$G = 1 + 50 \text{ k}\Omega / R_G$	1, 8
INA819	35- μ V Offset, 0.4 μ V/ $^{\circ}$ C V_{OS} Drift, 8-nV/ $\sqrt{\text{Hz}}$ Noise, Low-Power, Precision Instrumentation Amplifier	$G = 1 + 50 \text{ k}\Omega / R_G$	2, 3
INA821	35- μ V Offset, 0.4 μ V/ $^{\circ}$ C V_{OS} Drift, 7-nV/ $\sqrt{\text{Hz}}$ Noise, High-Bandwidth, Precision Instrumentation Amplifier	$G = 1 + 49.4 \text{ k}\Omega / R_G$	2, 3
INA828	50- μ V Offset, 0.5 μ V/ $^{\circ}$ C V_{OS} Drift, 7-nV/ $\sqrt{\text{Hz}}$ Noise, Low-Power, Precision Instrumentation Amplifier	$G = 1 + 50 \text{ k}\Omega / R_G$	1, 8
INA333	25- μ V V_{OS} , 0.1 μ V/ $^{\circ}$ C V_{OS} Drift, 1.8-V to 5-V, RRO, 50- μ A I_Q , Chopper-Stabilized INA	$G = 1 + 100 \text{ k}\Omega / R_G$	1, 8
PGA280	20-mV to ± 10 -V Programmable Gain IA With 3-V or 5-V Differential Output; Analog Supply up to ± 18 V	Digital programmable	N/A
INA159	$G = 0.2$ V Differential Amplifier for ± 10 -V to 3-V and 5-V Conversion	$G = 0.2 \text{ V/V}$	N/A
PGA112	Precision Programmable Gain Op Amp With SPI	Digital programmable	N/A

6 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
–IN	2	I	Negative (inverting) input
+IN	3	I	Positive (noninverting) input
OUT	6	O	Output
REF	5	I	Reference input. This pin must be driven by a low-impedance source.
RG	1, 8	—	Gain setting pin. Place a gain resistor between pin 1 and pin 8.
–VS	4	—	Negative supply
+VS	7	—	Positive supply

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

	MIN	MAX	UNIT
Supply voltage dual supply, $V_S = (V+) - (V-)$		±20	V
Supply voltage single supply, $V_S = (V+) - (V-)$		40, (single supply)	V
Signal input pins	–60	60	V
VREF pin	–20	20	V
Signal output pins maximum voltage	(– V_S) – 0.5	(+ V_S) + 0.5	V
Signal output pins maximum current	–50	50	mA
Output short-circuit ⁽²⁾	Continuous		
Operating Temperature, T_A	–50	150	°C
Junction Temperature, T_J		175	
Storage Temperature, T_{stg}	–65	150	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Short-circuit to $V_S / 2$.

7.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±1500
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±750

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Supply voltage V_S	Single-supply	4.5	36	V
	Dual-supply	±2.25	±18	
Specified temperature	Specified temperature	–40	125	°C

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		INA818	UNIT
		D (SOIC)	
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	119.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	66.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	61.9	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	20.5	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	61.4	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

7.5 Electrical Characteristics

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{ V}$, $R_L = 10\text{ k}\Omega$, $V_{\text{REF}} = 0\text{ V}$, and $G = 1$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
INPUT						
V _{OSI}	Input stage offset voltage ⁽¹⁾⁽²⁾			10	35	μV
		T _A = −40°C to 125°C ⁽³⁾			75	μV
		drift vs temperature, T _A = −40°C to 125°C			0.4	μV/°C
V _{OSO}	Output stage offset voltage ⁽¹⁾⁽²⁾			50	300	μV
		T _A = −40°C to 125°C ⁽³⁾			800	μV
		drift vs temperature, T _A = −40°C to 125°C			5	μV/°C
PSRR	Power-supply rejection ratio	G = 1, RTI	110	120		dB
		G = 10, RTI	114	130		
		G = 100, RTI	130	135		
		G = 1000, RTI	136	140		
Z _{id}	Differential impedance			100 1		GΩ pF
Z _{ic}	Common-mode impedance			100 4		GΩ pF
	RFI filter, −3-dB frequency			32		MHz
V _{CM}	Operating input range ⁽⁴⁾		(V−) + 2		(V+) − 2	V
		V _S = ±2.25 V to ±18 V, T _A = −40°C to 125°C	See Figure 51 to Figure 54			
	Input overvoltage range	T _A = −40°C to 125°C ⁽³⁾			±60	V
CMRR	Common-mode rejection ratio	At DC to 60 Hz, RTI, V _{CM} = (V−) + 2 V to (V+) − 2 V, G = 1	90	105		dB
		At DC to 60 Hz, RTI, V _{CM} = (V−) + 2 V to (V+) − 2 V, G = 10	110	125		
		At DC to 60 Hz, RTI, V _{CM} = (V−) + 2 V to (V+) − 2 V, G = 100	130	145		
		At DC to 60 Hz, RTI, V _{CM} = (V−) + 2 V to (V+) − 2 V, G = 1000	140	150		
BIAS CURRENT						
I _B	Input bias current	V _{CM} = V _S / 2		0.15	0.5	nA
		T _A = −40°C to 125°C			2	
I _{OS}	Input offset current	V _{CM} = V _S / 2		0.15	0.5	nA
		T _A = −40°C to 125°C			2	
NOISE VOLTAGE						
e _{NI}	Input stage voltage noise ⁽⁵⁾	f = 1 kHz, G = 100, R _S = 0 Ω		8		nV/√Hz
		f _B = 0.1 Hz to 10 Hz, G = 100, R _S = 0 Ω		0.19		μV _{PP}
e _{NO}	Output stage voltage noise ⁽⁵⁾	f = 1 kHz, R _S = 0 Ω		80		nV/√Hz
		f _B = 0.1 Hz to 10 Hz, R _S = 0 Ω		2.6		μV _{PP}
I _n	Noise current	f = 1 kHz		130		fA/√Hz
		f _B = 0.1 Hz to 10 Hz, G = 100		4.7		pA _{PP}
GAIN						
	Gain equation		1 + (50 kΩ / R _G)			V/V
G	Gain		1		1000	V/V
GE	Gain error	G = 1, V _O = ±10 V		±0.005%	±0.025%	
		G = 10, V _O = ±10 V		±0.025%	±0.15%	
		G = 100, V _O = ±10 V		±0.025%	±0.15%	
		G = 1000, V _O = ±10 V		±0.05%		
	Gain error drift ⁽⁶⁾	G = 1, T _A = −40°C to 125°C, V _O = ±10 V			±5	ppm/°C
		G > 1, T _A = −40°C to 125°C, V _O = ±10 V			±35	

(1) Total offset, referred-to-input (RTI): $V_{\text{OS}} = (V_{\text{OSI}}) + (V_{\text{OSO}} / G)$.

(2) Offset drifts are uncorrelated. Input-referred offset drift is calculated using: $\Delta V_{\text{OS(RTI)}} = \sqrt{[\Delta V_{\text{OSI}}]^2 + (\Delta V_{\text{OSO}} / G)^2}$

(3) Specified by characterization.

(4) Input voltage range of the INA818 input stage. The input range depends on the common-mode voltage, differential voltage, gain, and reference voltage. See *Typical Characteristic* curves [Figure 51](#) through [Figure 54](#) for more information.

(5) Total RTI voltage noise is equal to: $e_{\text{N(RTI)}} = \sqrt{[e_{\text{NI}}]^2 + (e_{\text{NO}} / G)^2}$

(6) The values specified for $G > 1$ do not include the effects of the external gain-setting resistor, R_G .

Electrical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{ V}$, $R_L = 10\text{ k}\Omega$, $V_{REF} = 0\text{ V}$, and $G = 1$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Gain nonlinearity	G = 1 to 10, V _O = −10 V to 10 V, R _L = 10 kΩ		1	10	ppm
		G = 100, V _O = −10 V to 10 V, R _L = 10 kΩ			15	
		G = 1000, V _O = −10 V to 10 V, R _L = 10 kΩ		10		
		G = 1 to 100, V _O = −10 V to 10 V, R _L = 2 kΩ		30		
OUTPUT						
	Voltage swing		(V−) + 0.15	(V+) − 0.15		V
	Load capacitance stability			1000		pF
Z _O	Closed-loop output impedance	f = 10 kHz		5.0		Ω
I _{SC}	Short-circuit current	Continuous to V _S / 2		±20		mA
FREQUENCY RESPONSE						
BW	Bandwidth, −3 dB	G = 1		2.0		MHz
		G = 10		890		kHz
		G = 100		270		
		G = 1000		30		
SR	Slew rate	G = 1, V _O = ±10 V		0.9		V/μs
t _s	Settling time	0.01%, G = 1 to 100, V _{STEP} = 10 V		12		μs
		0.01%, G = 1000, V _{STEP} = 10 V		40		
		0.001%, G = 1 to 100, V _{STEP} = 10 V		16		
		0.001%, G = 1000, V _{STEP} = 10 V		60		
REFERENCE INPUT						
R _{IN}	Input impedance			40		kΩ
	Voltage range		(V−)	(V+)		V
	Gain to output			1		V/V
	Reference gain error			0.01%		
POWER SUPPLY						
I _Q	Quiescent current	V _{IN} = 0 V		350	385	μA
		V _{IN} = 0 V, T _A = −40°C to 125°C			520	

7.6 Typical Characteristics: Table of Graphs

表 1. Table of Graphs

DESCRIPTION	FIGURE
Typical Distribution of Input Stage Offset Voltage	Figure 1
Typical Distribution of Input Stage Offset Voltage Drift	Figure 2
Typical Distribution of Output Stage Offset Voltage	Figure 3
Typical Distribution of Output Stage Offset Voltage Drift	Figure 4
Input Stage Offset Voltage vs Temperature	Figure 5
Output Stage Offset Voltage vs Temperature	Figure 6
Typical Distribution of Input Bias Current $T_A = 25^\circ\text{C}$	Figure 7
Typical Distribution of Input Bias Current $T_A = 90^\circ\text{C}$	Figure 8
Typical Distribution of Input Offset Current	Figure 9
Input Bias Current vs Temperature	Figure 10
Input Offset Current vs Temperature	Figure 11
Typical CMRR Distribution $G = 1$	Figure 12
Typical CMRR Distribution $G = 10$	Figure 13
CMRR vs Temperature $G = 1$	Figure 14
CMRR vs Temperature $G = 10$	Figure 15
Input Current vs Input Overvoltage	Figure 16
CMRR vs Frequency (RTI)	Figure 17
CMRR vs Frequency (RTI, 1-k Ω source imbalance)	Figure 18
Positive PSRR vs Frequency (RTI)	Figure 19
Negative PSRR vs Frequency (RTI)	Figure 20
Gain vs Frequency	Figure 21
Voltage Noise Spectral Density vs Frequency (RTI)	Figure 22
Current Noise Spectral Density vs Frequency (RTI)	Figure 23
0.1-Hz to 10-Hz RTI Voltage Noise $G = 1$	Figure 24
0.1-Hz to 10-Hz RTI Voltage Noise $G = 1000$	Figure 25
0.1-Hz to 10-Hz RTI Current Noise	Figure 26
Typical Distribution of Gain Error $G = 1$	Figure 28
Typical Distribution of Gain Error $G = 10$	Figure 29
Input Bias Current vs Common-Mode Voltage	Figure 27
Gain Error vs Temperature $G = 1$	Figure 30
Gain Error vs Temperature $G = 10$	Figure 31
Supply Current vs Temperature	Figure 32
Gain Nonlinearity $G = 1$	Figure 33
Gain Nonlinearity $G = 10$	Figure 34
Offset Voltage vs Negative Common-Mode Voltage	Figure 35
Offset Voltage vs Positive Common-Mode Voltage	Figure 36
Positive Output Voltage Swing vs Output Current	Figure 37
Negative Output Voltage Swing vs Output Current	Figure 38
Short Circuit Current vs Temperature	Figure 39
Large-Signal Frequency Response	Figure 40
THD+N vs Frequency	Figure 41
Overshoot vs Capacitive Loads	Figure 42
Small-Signal Response $G = 1$	Figure 43
Small-Signal Response $G = 10$	Figure 44
Small-Signal Response $G = 100$	Figure 45
Small-Signal Response $G = 1000$	Figure 46

Typical Characteristics: Table of Graphs (continued)
表 1. Table of Graphs (continued)

DESCRIPTION	FIGURE
Large Signal Step Response	Figure 47
Closed-Loop Output Impedance	Figure 48
Differential-Mode EMI Rejection Ratio	Figure 49
Common-Mode EMI Rejection Ratio	Figure 50
Input Common-Mode Voltage vs Output Voltage $G = 1$, $V_S = 5\text{ V}$	Figure 51
Input Common-Mode Voltage vs Output Voltage $G = 100$, $V_S = 5\text{ V}$	Figure 52
Input Common-Mode Voltage vs Output Voltage $V_S = \pm 5\text{ V}$	Figure 53
Input Common-Mode Voltage vs Output Voltage $V_S = \pm 15\text{ V}$	Figure 54

7.7 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{ V}$, $R_L = 10\text{ k}\Omega$, $V_{\text{REF}} = 0\text{ V}$, and $G = 1$ (unless otherwise noted)

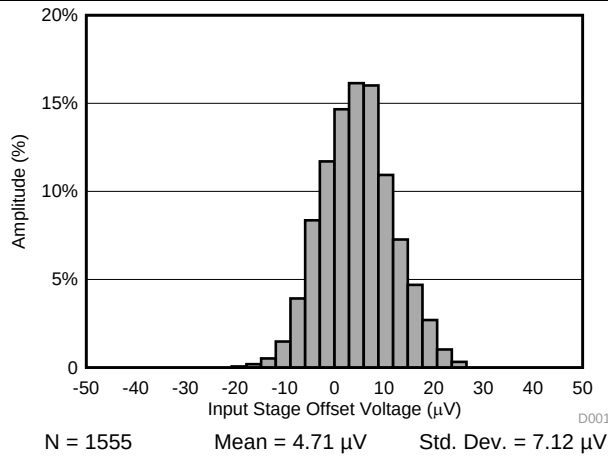


图 1. Typical Distribution of Input Stage Offset Voltage

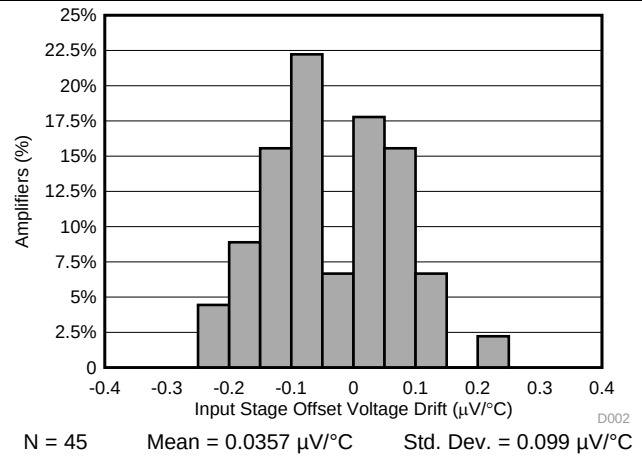


图 2. Typical Distribution of Input Stage Offset Voltage Drift

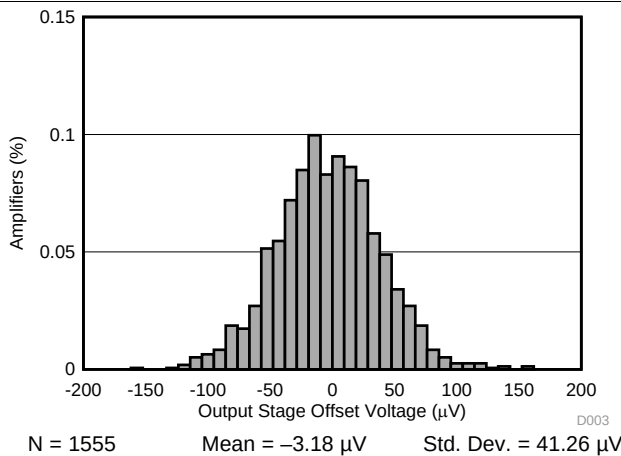


图 3. Typical Distribution of Output Stage Offset Voltage

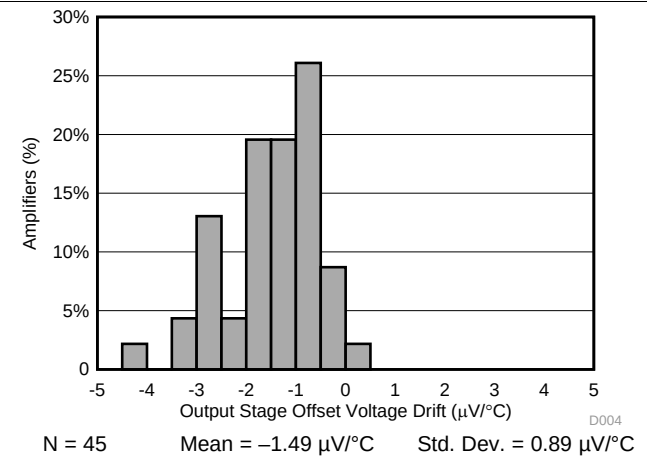


图 4. Typical Distribution of Output Stage Offset Voltage Drift

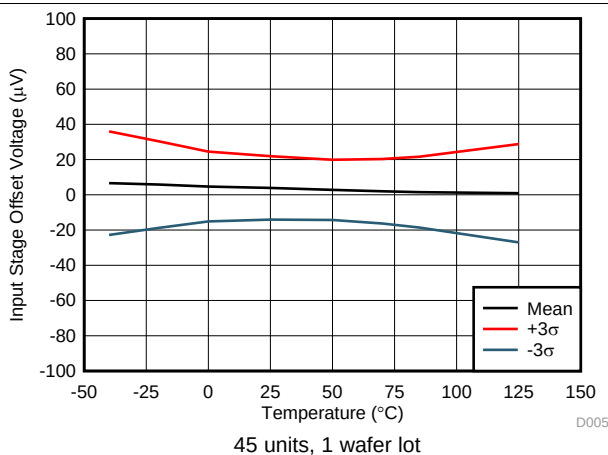


图 5. Input Stage Offset Voltage vs Temperature

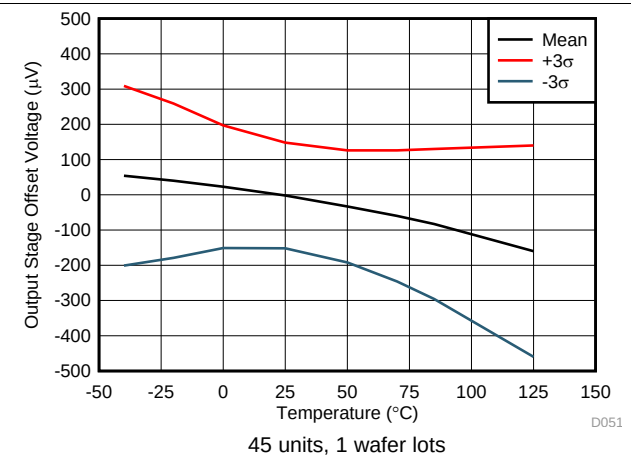


图 6. Output Stage Offset Voltage vs Temperature

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{ V}$, $R_L = 10\text{ k}\Omega$, $V_{\text{REF}} = 0\text{ V}$, and $G = 1$ (unless otherwise noted)

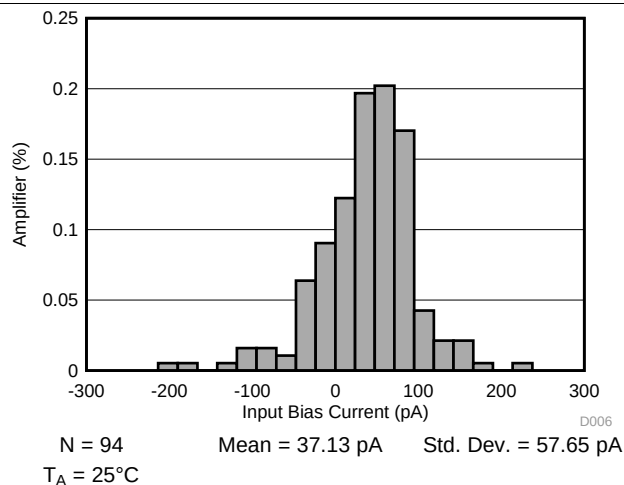


Figure 7. Typical Distribution of Input Bias Current

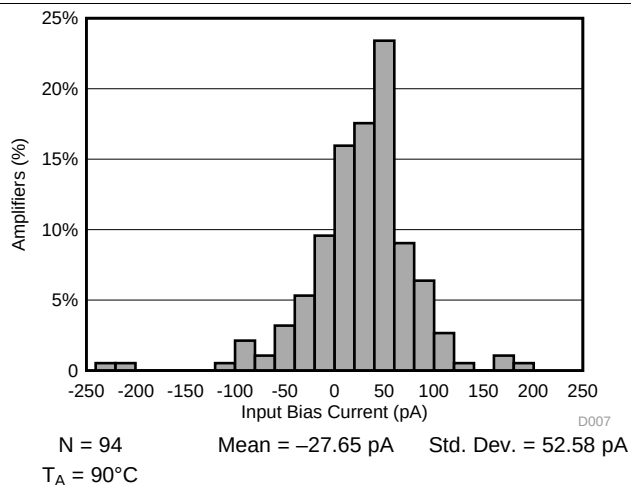


Figure 8. Typical Distribution of Input Bias Current

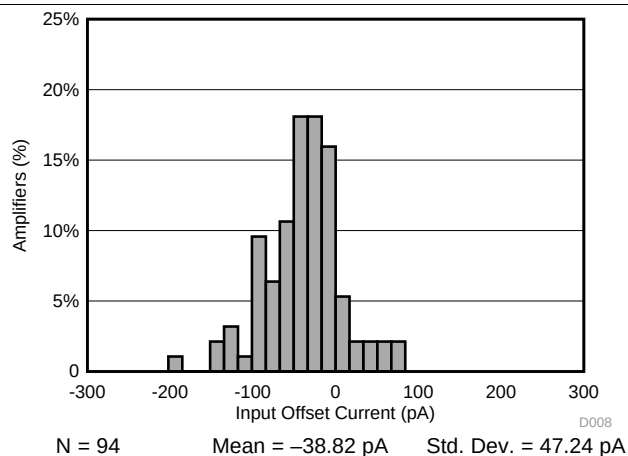


Figure 9. Typical Distribution of Input Offset Current

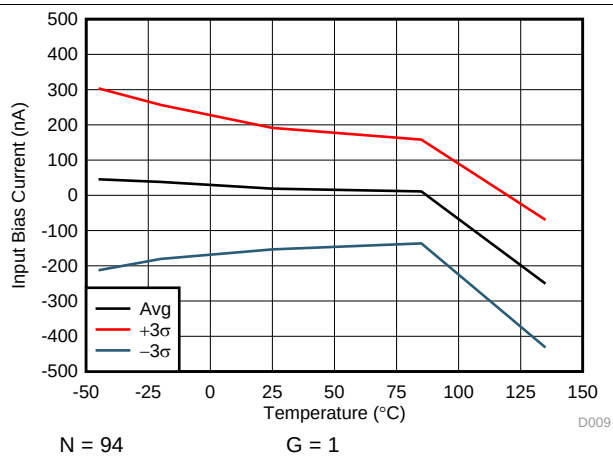


Figure 10. Input Bias Current vs Temperature

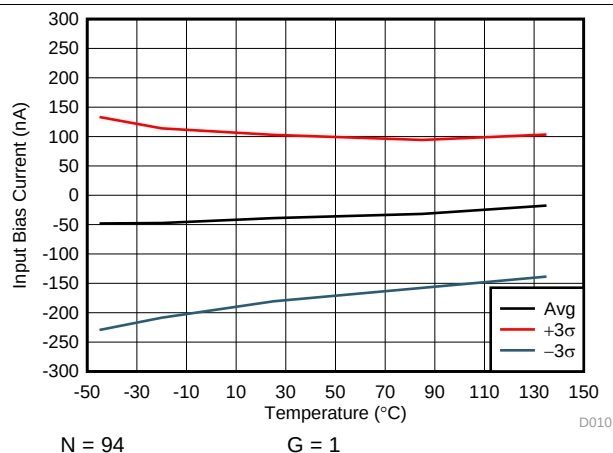


Figure 11. Input Offset Current vs Temperature

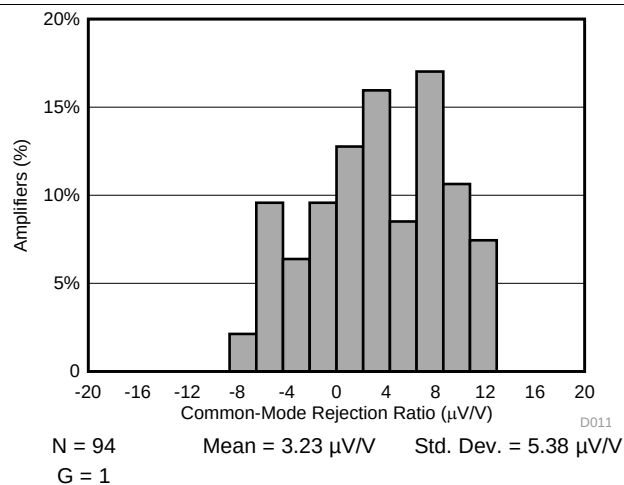


Figure 12. Typical CMRR Distribution

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{ V}$, $R_L = 10\text{ k}\Omega$, $V_{\text{REF}} = 0\text{ V}$, and $G = 1$ (unless otherwise noted)

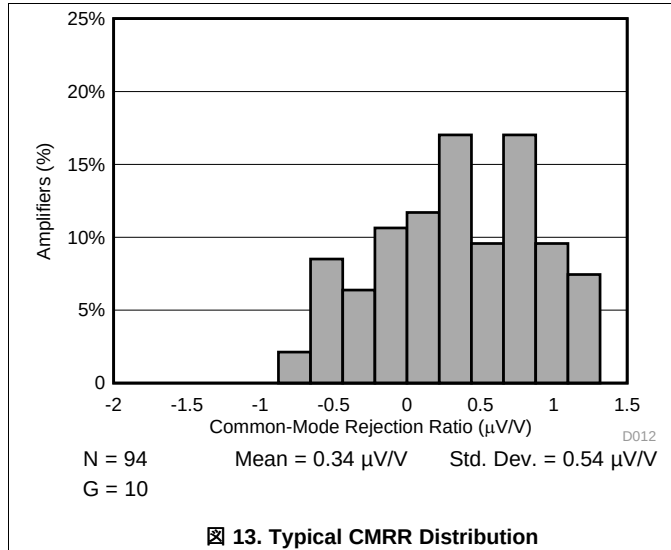


Figure 13. Typical CMRR Distribution

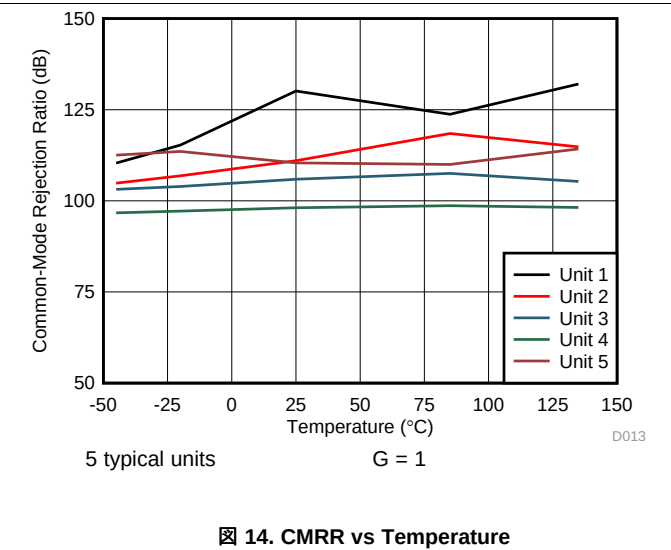


Figure 14. CMRR vs Temperature

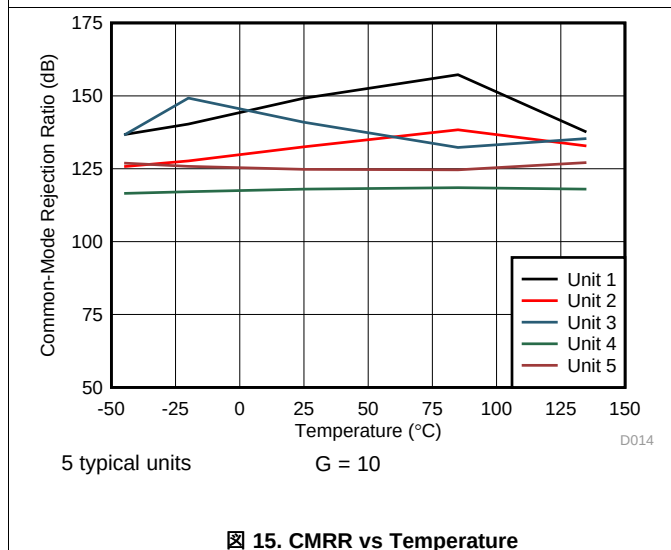


Figure 15. CMRR vs Temperature

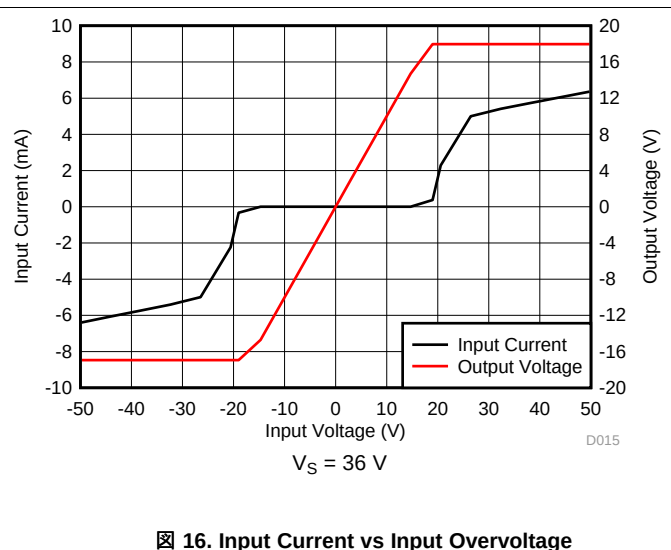


Figure 16. Input Current vs Input Overvoltage

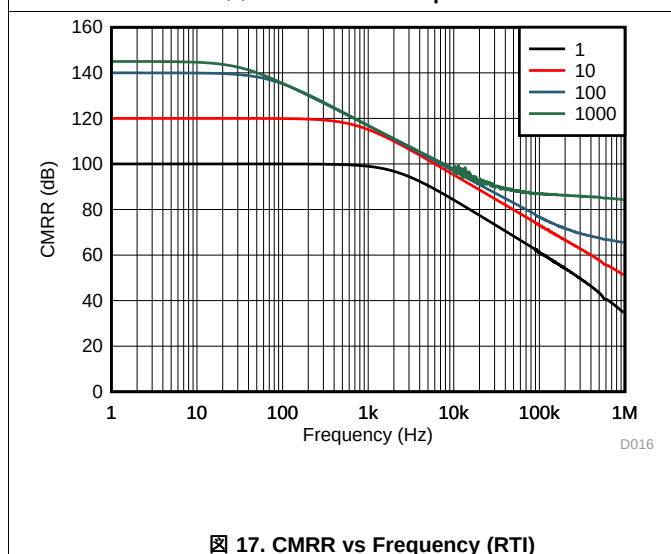


Figure 17. CMRR vs Frequency (RTI)

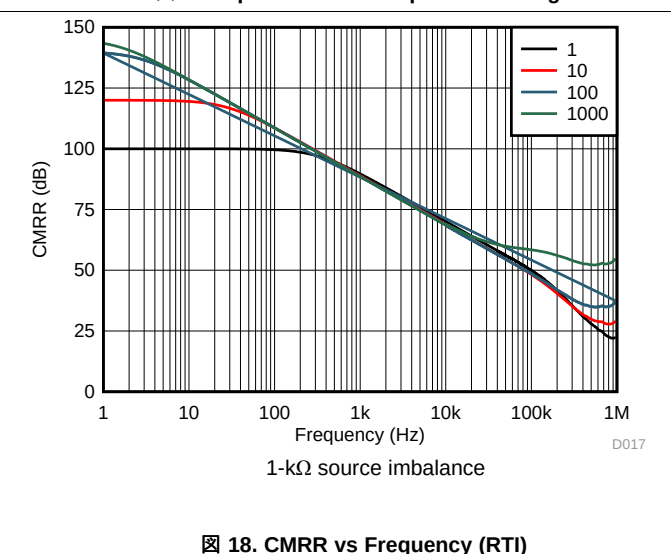


Figure 18. CMRR vs Frequency (RTI)

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{ V}$, $R_L = 10\text{ k}\Omega$, $V_{\text{REF}} = 0\text{ V}$, and $G = 1$ (unless otherwise noted)

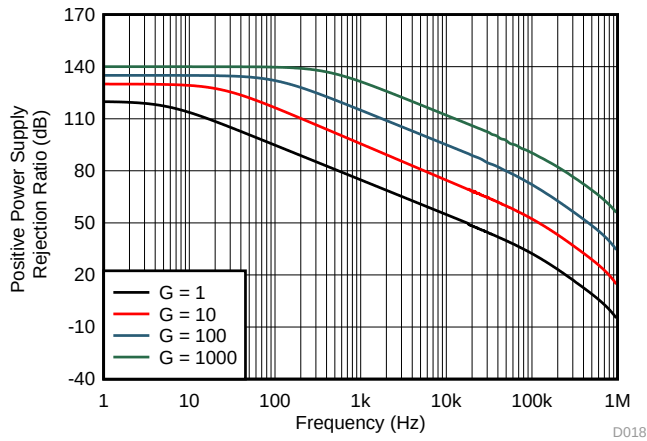


FIG 19. Positive PSRR vs Frequency (RTI)

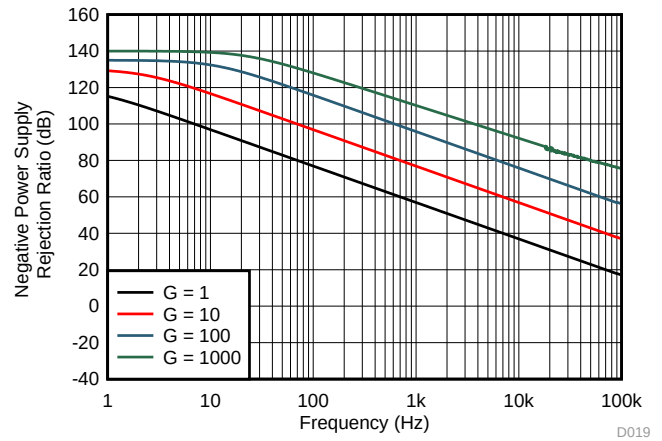


FIG 20. Negative PSRR vs Frequency (RTI)

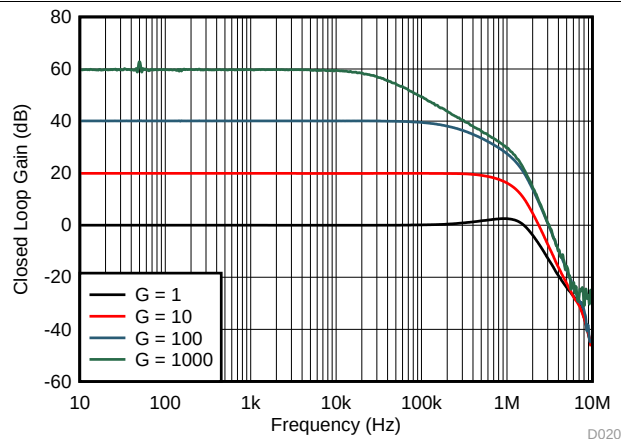


FIG 21. Gain vs Frequency

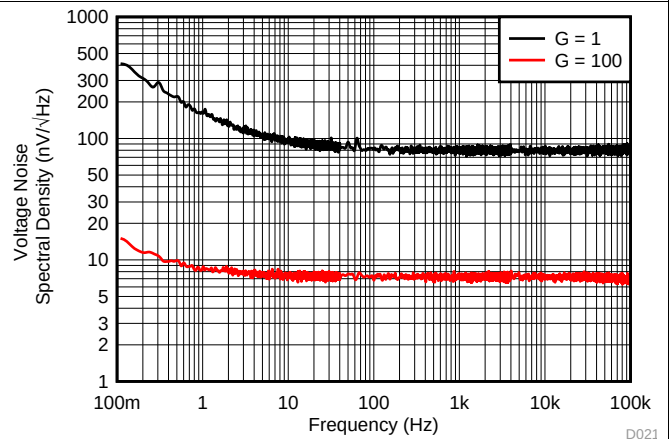


FIG 22. Voltage Noise Spectral Density vs Frequency (RTI)

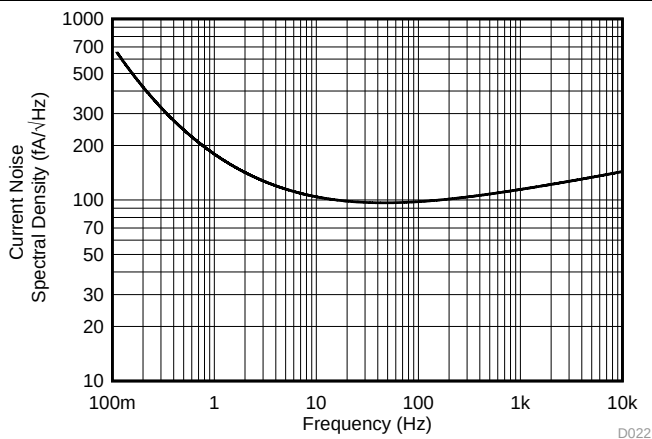


FIG 23. Current Noise Spectral Density vs Frequency (RTI)

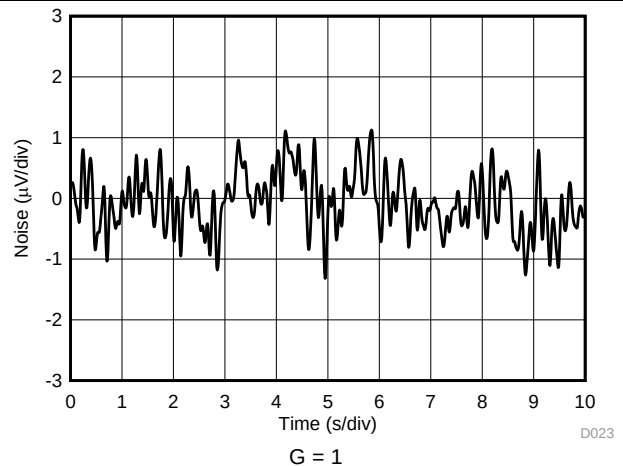


FIG 24. 0.1-Hz to 10-Hz RTI Voltage Noise

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{ V}$, $R_L = 10\text{ k}\Omega$, $V_{\text{REF}} = 0\text{ V}$, and $G = 1$ (unless otherwise noted)

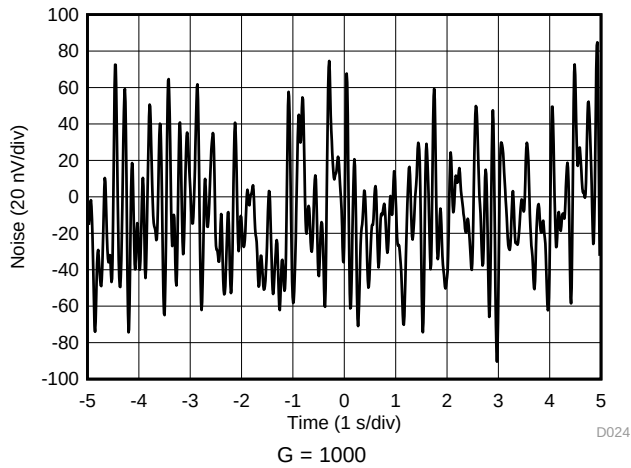


Figure 25. 0.1-Hz to 10-Hz RTI Voltage Noise

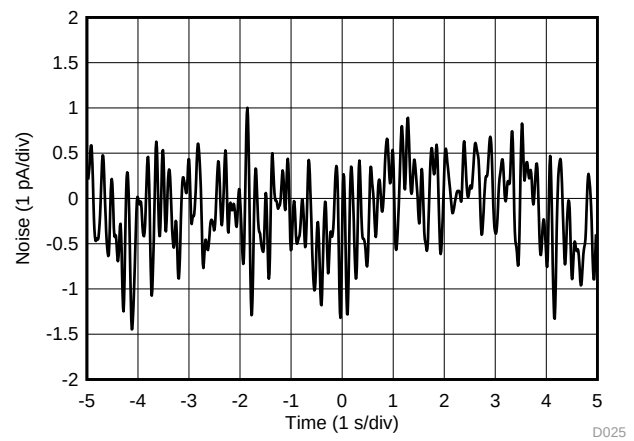


Figure 26. 0.1-Hz to 10-Hz RTI Current Noise

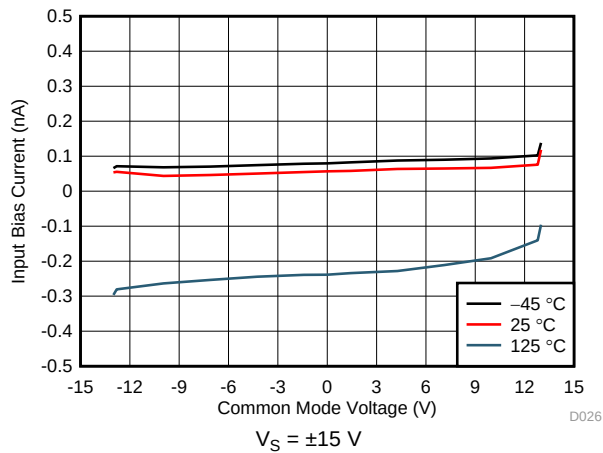


Figure 27. Input Bias Current vs Common-Mode Voltage

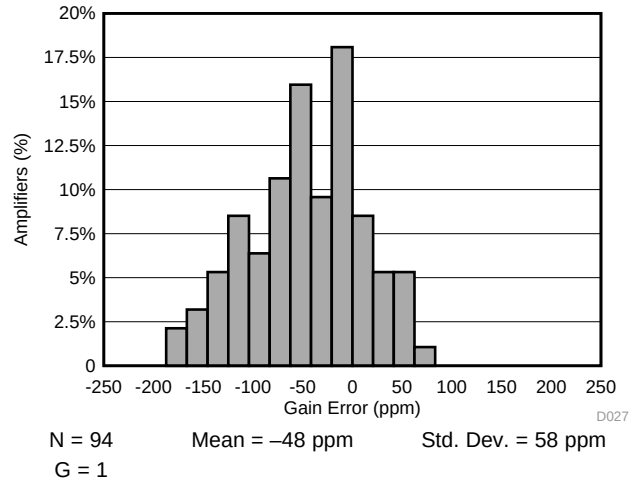


Figure 28. Typical Distribution of Gain Error $G = 1$

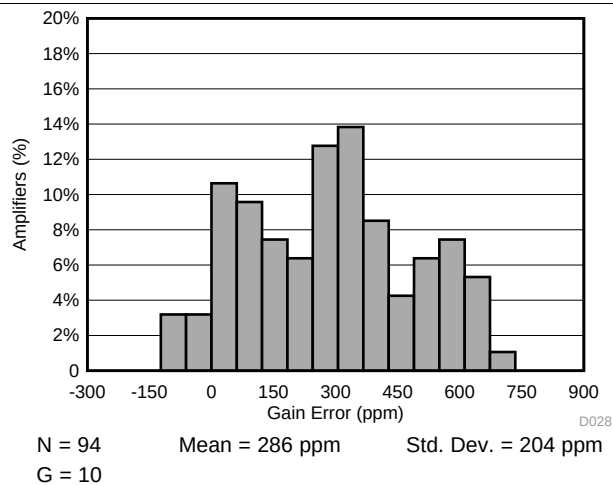


Figure 29. Typical Distribution of Gain Error $G = 10$

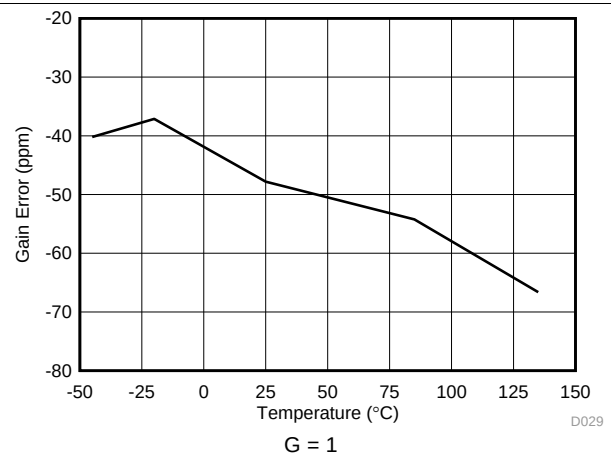


Figure 30. Gain Error vs Temperature

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{ V}$, $R_L = 10\text{ k}\Omega$, $V_{\text{REF}} = 0\text{ V}$, and $G = 1$ (unless otherwise noted)

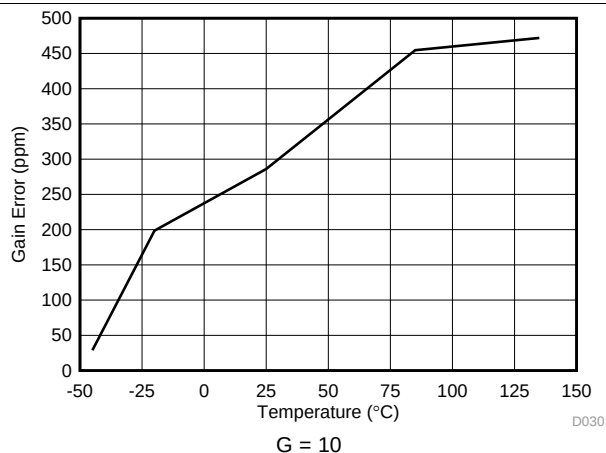


FIG 31. Gain Error vs Temperature

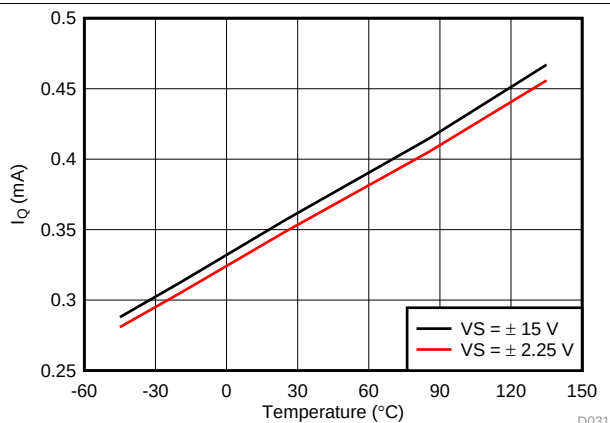


FIG 32. Supply Current vs Temperature

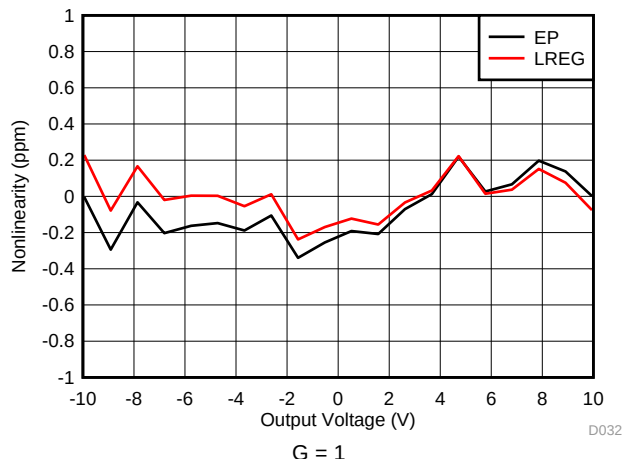


FIG 33. Gain Nonlinearity

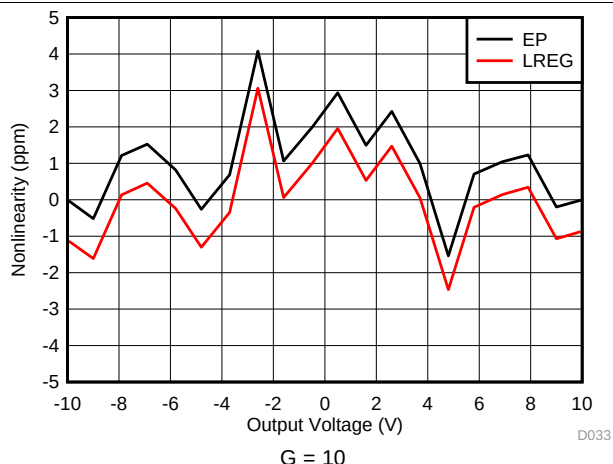


FIG 34. Gain Nonlinearity

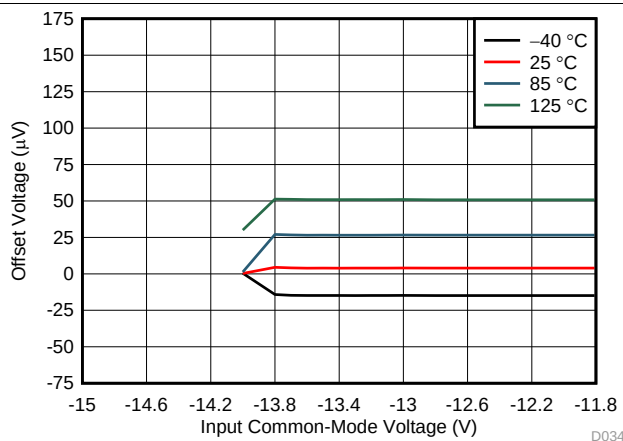


FIG 35. Offset Voltage vs Negative Common-Mode Voltage

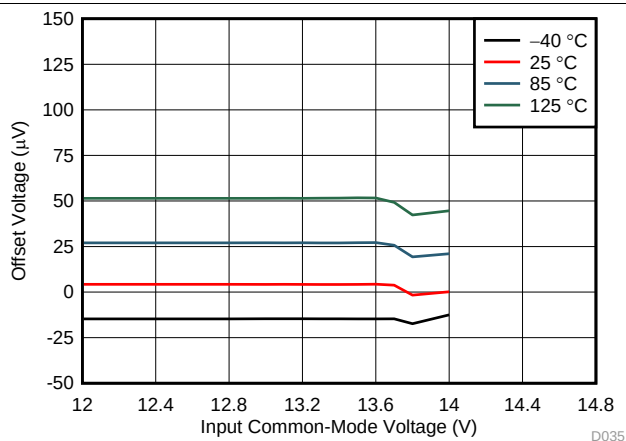
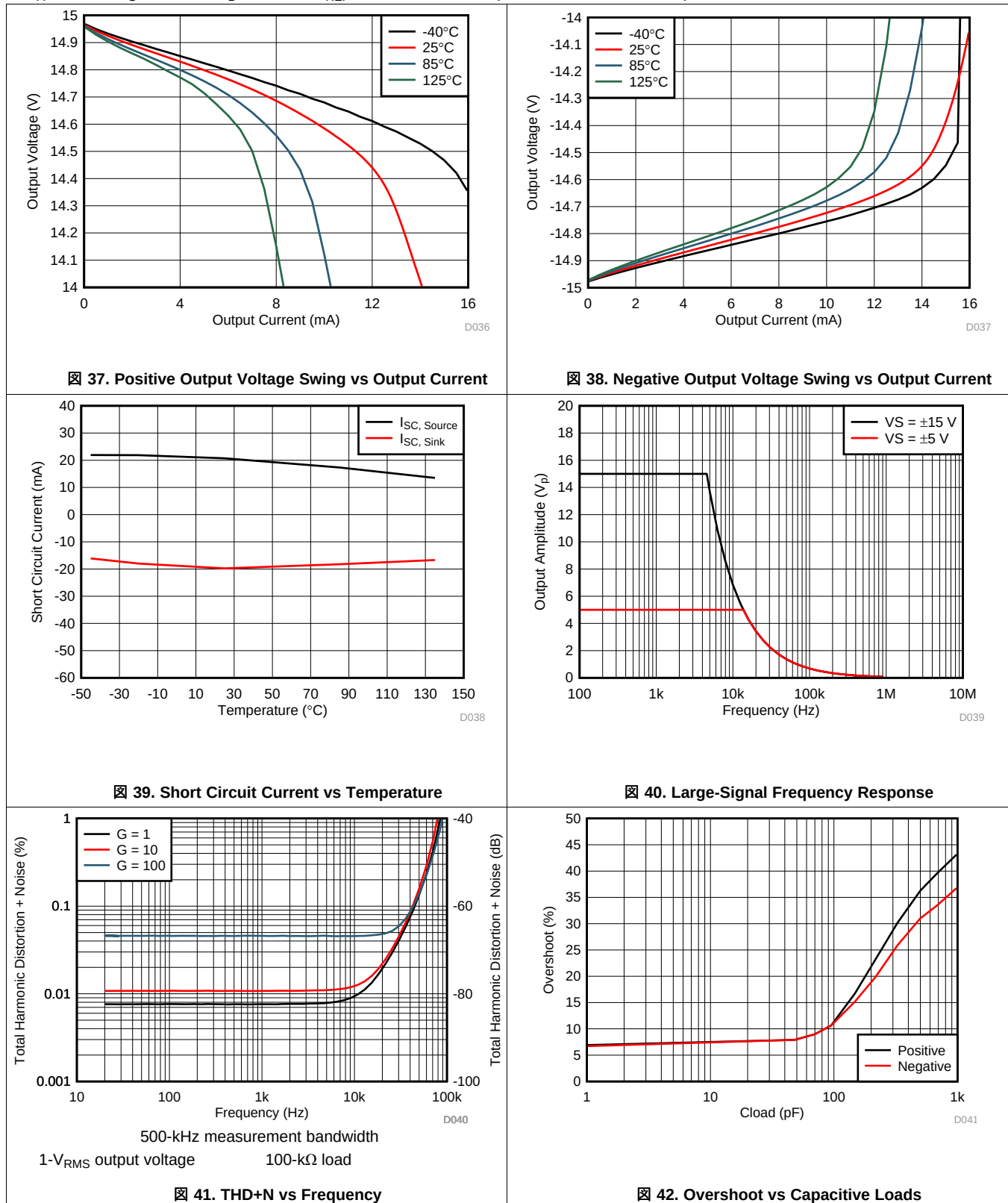


FIG 36. Offset Voltage vs Positive Common-Mode Voltage

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{ V}$, $R_L = 10\text{ k}\Omega$, $V_{\text{REF}} = 0\text{ V}$, and $G = 1$ (unless otherwise noted)



Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{ V}$, $R_L = 10\text{ k}\Omega$, $V_{\text{REF}} = 0\text{ V}$, and $G = 1$ (unless otherwise noted)

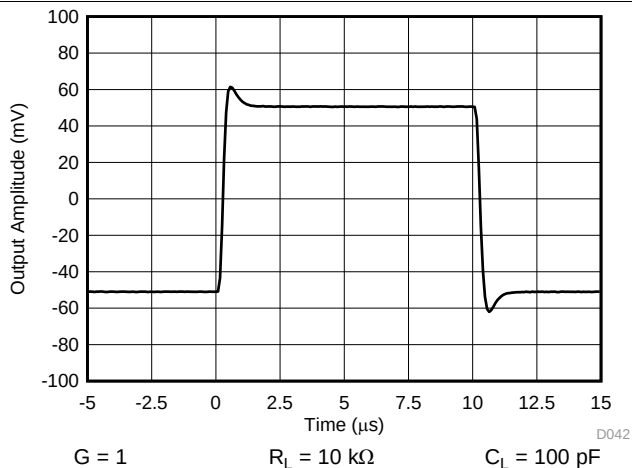


FIG 43. Small-Signal Response

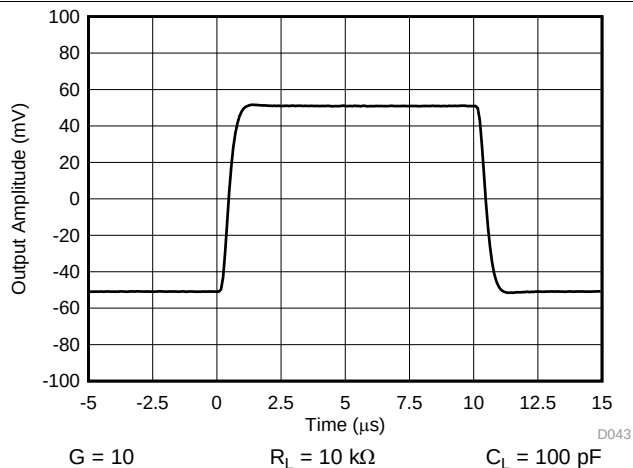


FIG 44. Small-Signal Response

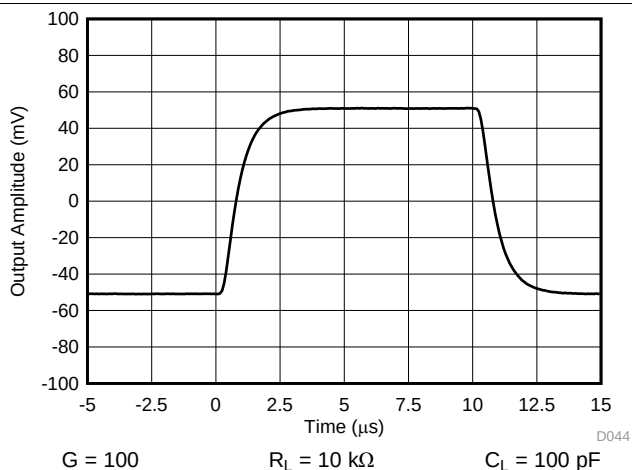


FIG 45. Small-Signal Response

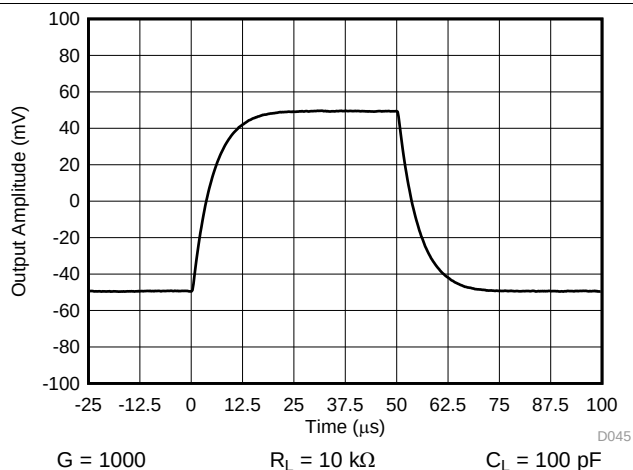


FIG 46. Small-Signal Response

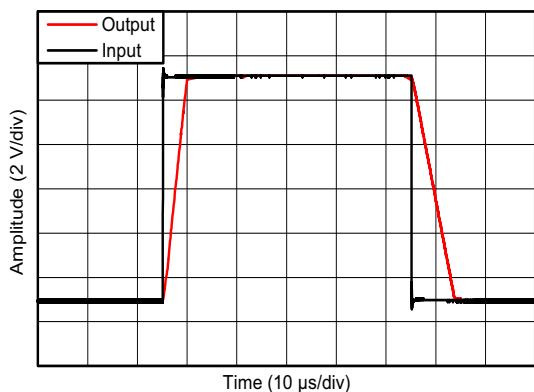


FIG 47. Large Signal Step Response

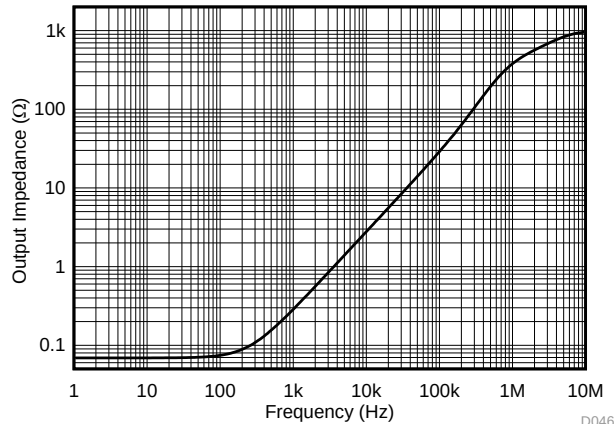


FIG 48. Closed-Loop Output Impedance

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{ V}$, $R_L = 10\text{ k}\Omega$, $V_{\text{REF}} = 0\text{ V}$, and $G = 1$ (unless otherwise noted)

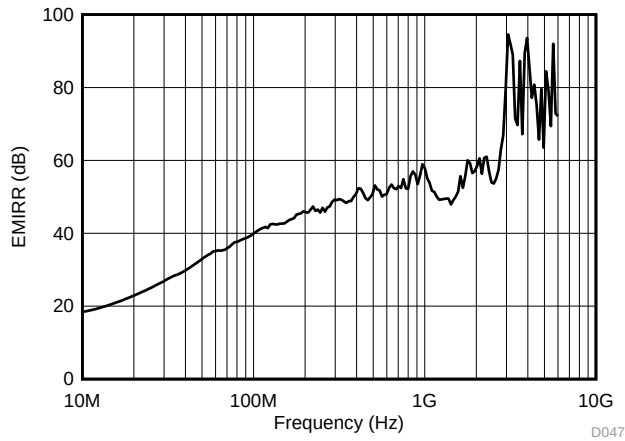


FIG 49. Differential-Mode EMI Rejection Ratio

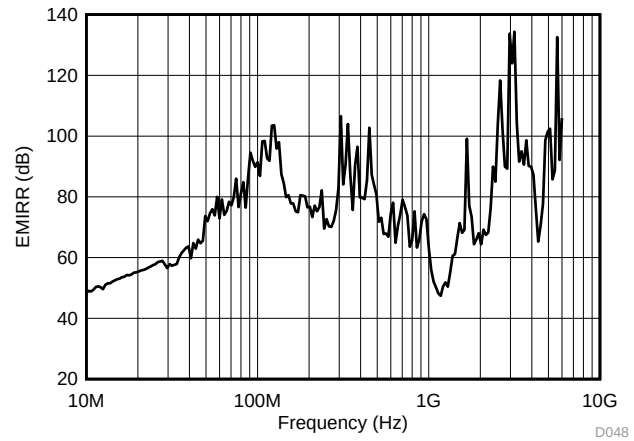


FIG 50. Common-Mode EMI Rejection Ratio

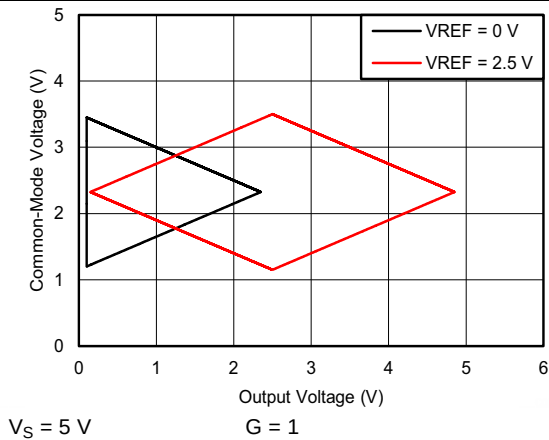


FIG 51. Input Common-Mode Voltage vs Output Voltage

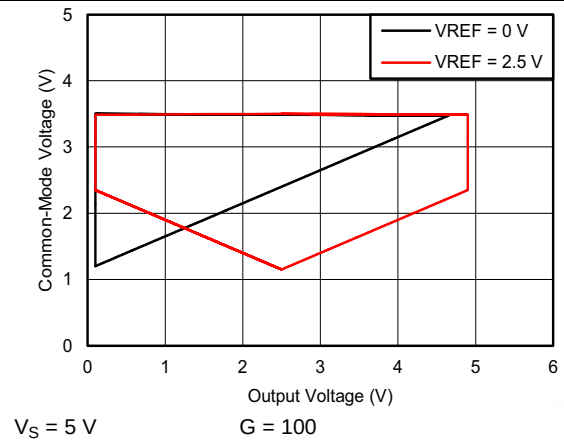


FIG 52. Input Common-Mode Voltage vs Output Voltage

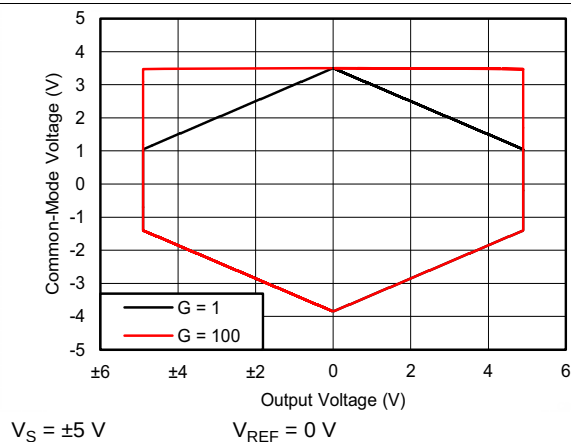


FIG 53. Input Common-Mode Voltage vs Output Voltage

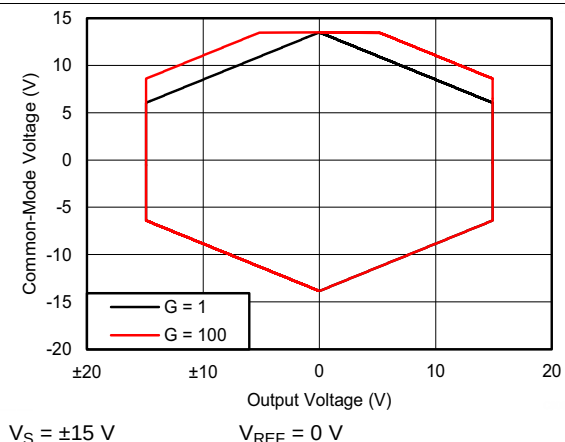


FIG 54. Input Common-Mode Voltage vs Output Voltage

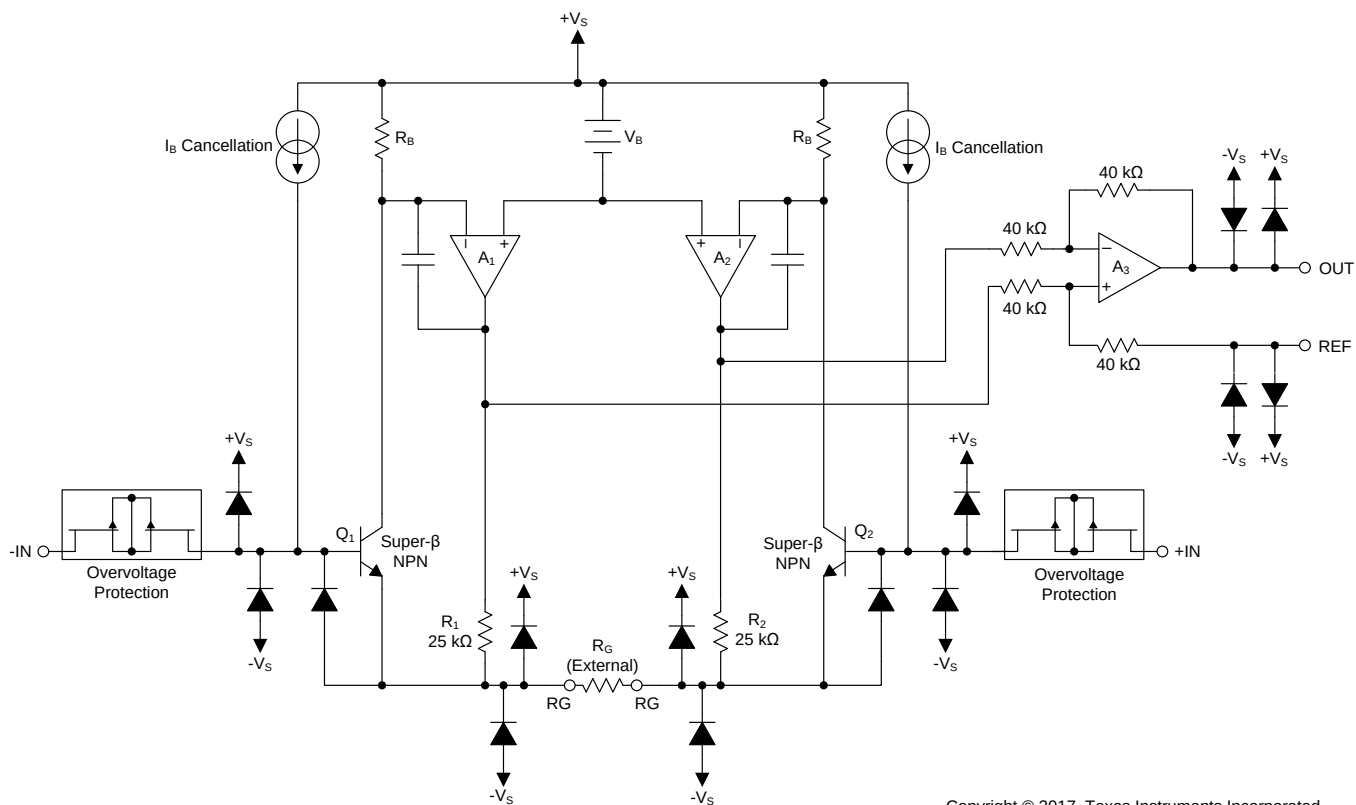
8 Detailed Description

8.1 Overview

The INA818 is a monolithic, precision instrumentation amplifier incorporating a current-feedback input stage and a four-resistor difference amplifier output stage. The functional block diagram in the next section shows how the differential input voltage is buffered by transistors Q_1 and Q_2 and is forced across resistor R_G , which causes a signal current to flow through resistors R_G , R_1 , and R_2 . The output difference amplifier, A_3 , removes the common-mode component of the input signal and refers the output signal to the REF pin. The V_{BE} and voltage drop across R_1 and R_2 produce output voltages on A_1 and A_2 that are approximately 0.8 V lower than the input voltages.

Each input is protected by two field-effect transistors (FETs) that provide a low series resistance under normal signal conditions, and preserve excellent noise performance. When excessive voltage is applied, these transistors limit input current to approximately 8 mA.

8.2 Functional Block Diagram



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8.3 Feature Description

8.3.1 Setting the Gain

Figure 55 shows that the gain of the INA818 is set by a single external resistor (R_G) connected between the RG pins (pins 1 and 8).

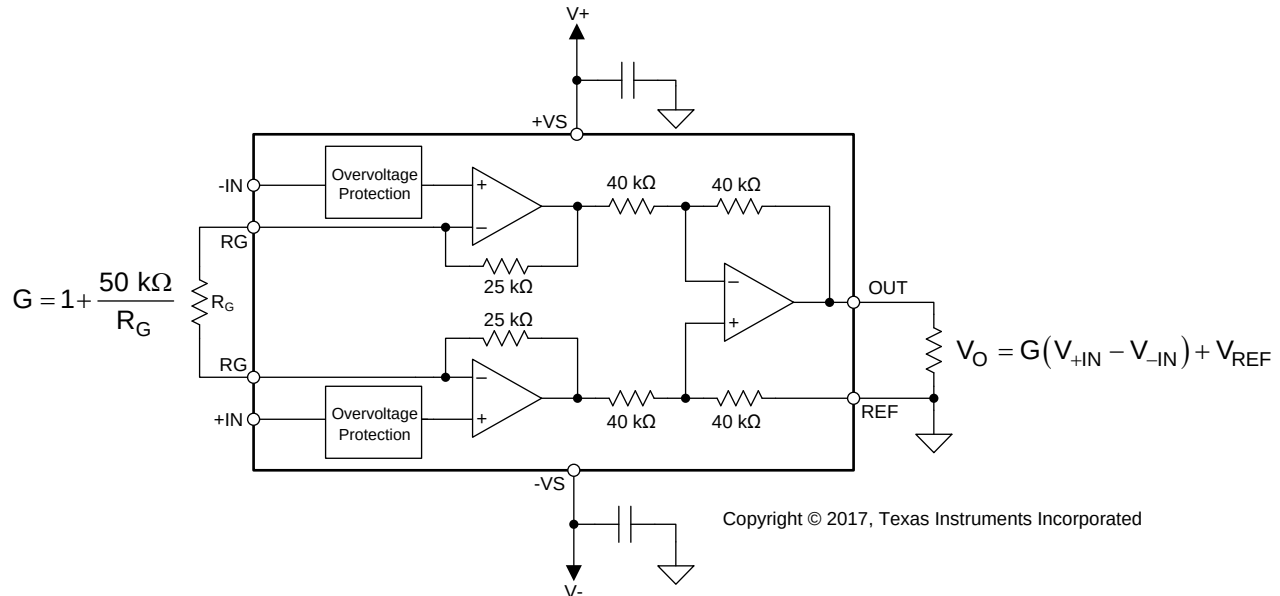


Figure 55. Simplified Diagram of the INA818 With Gain and Output Equations

The value of R_G is selected according to Equation 1:

$$G = 1 + \frac{50 \text{ k}\Omega}{R_G} \quad (1)$$

Table 2 lists several commonly-used gains and resistor values. The 50-kΩ term in Equation 1 comes from the sum of the two internal 25-kΩ feedback resistors. These on-chip resistors are laser-trimmed to accurate absolute values. The accuracy and temperature coefficients of these resistors are included in the gain accuracy and drift specifications of the INA818. As shown in Figure 55 and explained in more details in the Layout section, make sure to connect low-ESR, 0.1-μF ceramic bypass capacitors between each supply pin and ground that are placed as close to the device as possible.

Table 2. Commonly-Used Gains and Resistor Values

DESIRED GAIN	R_G (Ω)	NEAREST 1% R_G (Ω)
1	NC	NC
2	50 k	49.9 k
5	12.5 k	12.4 k
10	5.556 k	5.49 k
20	2.632 k	2.61 k
50	1.02 k	1.02 k
100	505.1	511
200	251.3	249
500	100.2	100
1000	50.05	49.9

8.3.1.1 Gain Drift

The stability and temperature drift of the external gain setting resistor (R_G) also affects gain. The contribution of R_G to gain accuracy and drift is determined from 式 1.

The best gain drift of 5 ppm/°C (maximum) is achieved when the INA818 uses $G = 1$ without R_G connected. In this case, gain drift is limited by the mismatch of the temperature coefficient of the integrated 40-kΩ resistors in the differential amplifier (A_3). At gains greater than 1, gain drift increases as a result of the individual drift of the 25-kΩ resistors in the feedback of A_1 and A_2 , relative to the drift of the external gain resistor (R_G .) The low temperature coefficient of the internal feedback resistors improves the overall temperature stability of applications using gains greater than 1 V/V over alternate solutions.

Low resistor values required for high gain make wiring resistance an important consideration. Sockets add to the wiring resistance and contribute additional gain error (such as a possible unstable gain error) at gains of approximately 100 or greater. To maintain stability, avoid parasitic capacitance of more than a few picofarads at R_G connections. Careful matching of any parasitics on the R_G pins maintains optimal CMRR over frequency.

8.3.2 EMI Rejection

Texas Instruments developed a method to accurately measure the immunity of an amplifier over a broad frequency spectrum extending from 10 MHz to 6 GHz. This method uses an EMI rejection ratio (EMIRR) to quantify the ability of the INA818 to reject EMI. The offset resulting from an input EMI signal is calculated using 式 2:

$$\Delta V_{OS} = \left(\frac{V_{RF_PEAK}^2}{100 \text{ mV}_P} \right) \cdot 10^{\left(\frac{EMIRR \text{ (dB)}}{20} \right)}$$

where

- V_{RF_PEAK} is the peak amplitude of the input EMI signal. (2)

Figure 56 and Figure 57 show the INA818 EMIRR graphs for differential and common-mode EMI rejection across this frequency range. Table 3 lists the EMIRR values for the INA818 at frequencies commonly encountered in real-world applications. Applications listed in Table 3 are centered on or operated near the frequency shown. Depending on the end-system requirements, additional EMI filters may be required near the signal inputs of the system. Incorporating known good practices, such as using short traces, low-pass filters, and damping resistors combined with parallel and shielded signal routing may also be required.

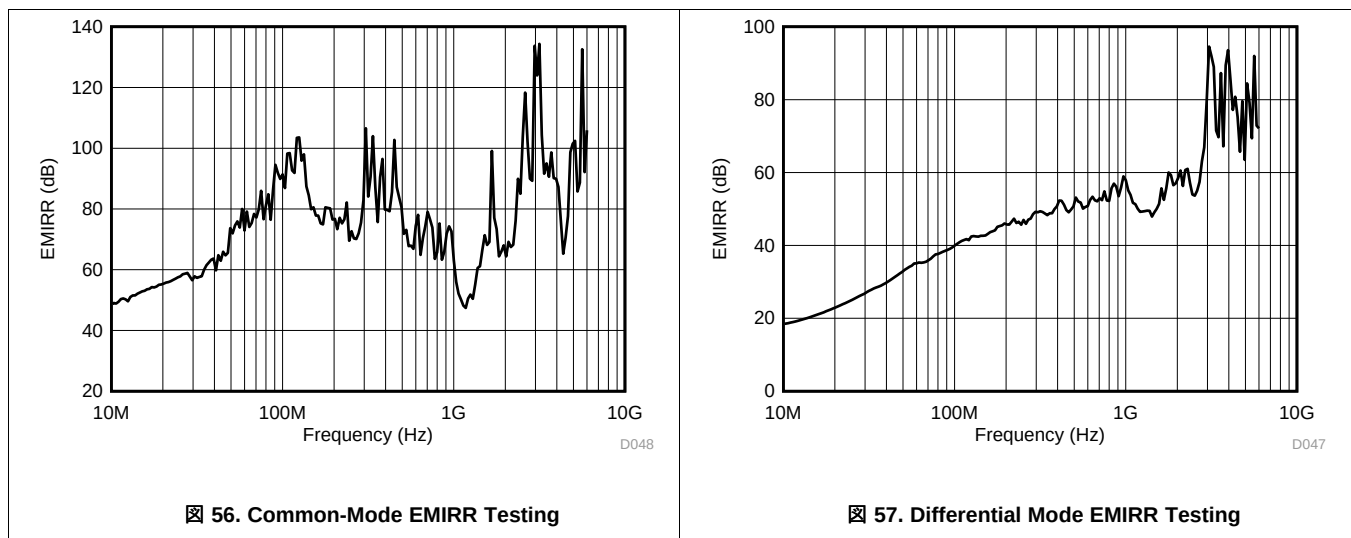
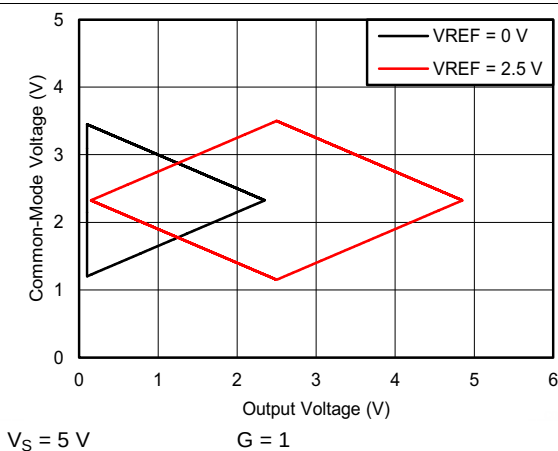
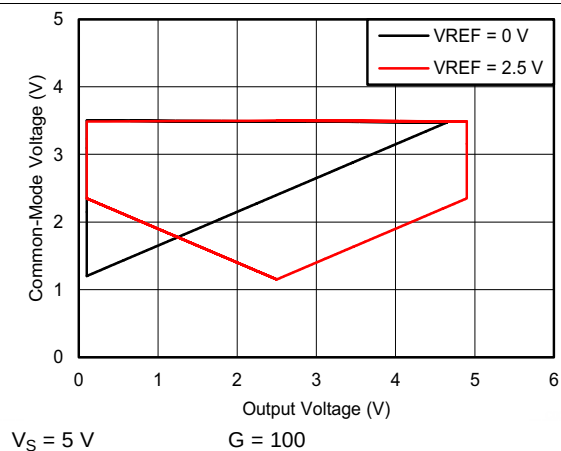
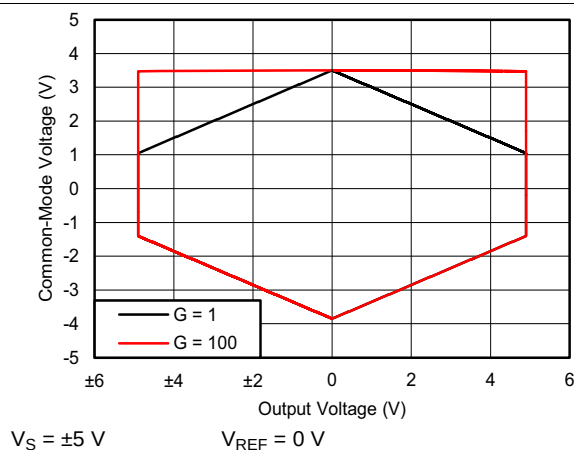
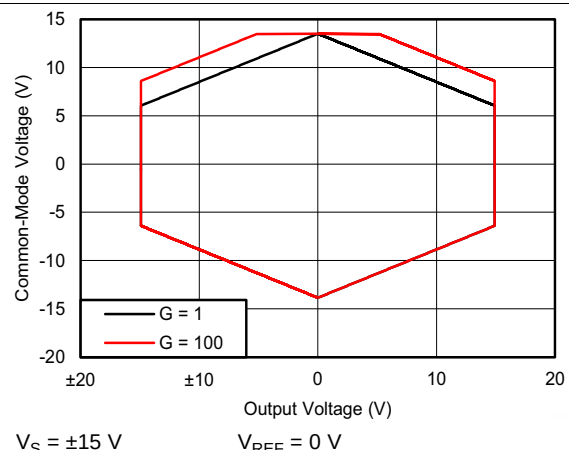


表 3. INA818 EMIRR for Frequencies of Interest

FREQUENCY	APPLICATION OR ALLOCATION	DIFFERENTIAL EMIRR	COMMON-MODE EMIRR
400 MHz	Mobile radio, mobile satellite, space operation, weather, radar, ultrahigh-frequency (UHF) applications	52 dB	80 dB
900 MHz	Global system for mobile communications (GSM) applications, radio communication, navigation, GPS (up to 1.6 GHz), GSM, aeronautical mobile, UHF applications	55 dB	71 dB
1.8 GHz	GSM applications, mobile personal communications, broadband, satellite, L-band (1 GHz to 2 GHz)	58 dB	73 dB
2.4 GHz	802.11b, 802.11g, 802.11n, Bluetooth®, mobile personal communications, industrial, scientific and medical (ISM) radio band, amateur radio and satellite, S-band (2 GHz to 4 GHz)	59 dB	95 dB
3.6 GHz	Radiolocation, aero communication and navigation, satellite, mobile, S-band	78 dB	96 dB
5 GHz	802.11a, 802.11n, aero communication and navigation, mobile communication, space and satellite operation, C-band (4 GHz to 8 GHz)	70 dB	100 dB

8.3.3 Input Common-Mode Range

The linear input voltage range of the INA818 input circuitry extends within 1.5 V (typical) of both power supplies and maintains excellent common-mode rejection throughout this range. The common-mode range for the most common operating conditions are shown in [Figure 58](#), [Figure 53](#), and [Figure 54](#). The common-mode range for other operating conditions is best calculated using the [Common-Mode Input Range Calculator for Instrumentation Amplifiers](#).


Figure 58. Input Common-Mode Voltage vs Output Voltage

Figure 59. Input Common-Mode Voltage vs Output Voltage

Figure 60. Input Common-Mode Voltage vs Output Voltage

Figure 61. Input Common-Mode Voltage vs Output Voltage

8.3.4 Input Protection

The inputs of the INA818 device are individually protected for voltages up to ± 60 V. For example, a condition of -60 V on one input and $+60$ V on the other input does not cause damage. Internal circuitry on each input provides low series impedance under normal signal conditions. If the input is overloaded, the protection circuitry limits the input current to a value of approximately 8 mA.

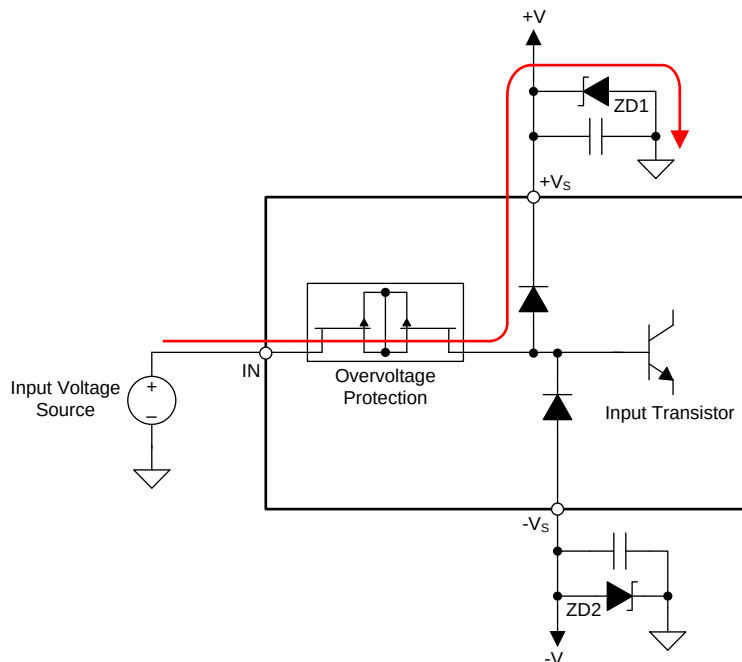


FIG 62. Input Current Path During an Overvoltage Condition

During an input overvoltage condition, current flows through the input protection diodes into the power supplies; see FIG 62. If the power supplies are unable to sink current, then Zener diode clamps (ZD1 and ZD2 in FIG 62) must be placed on the power supplies to provide a current pathway to ground. FIG 63 shows the input current for input voltages from -50 V to $+50$ V when the INA818 is powered by ± 15 -V supplies.

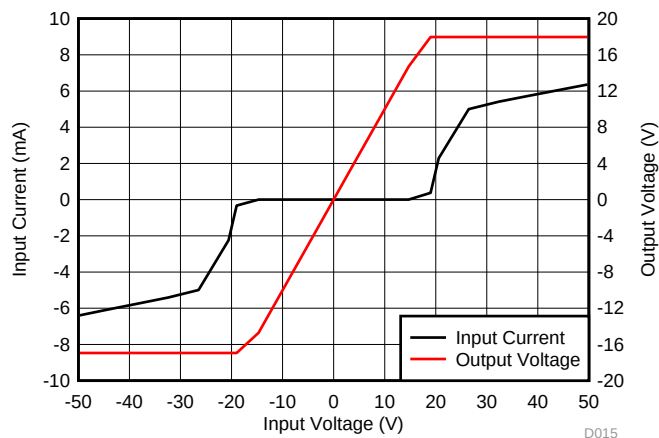


FIG 63. Input Current vs Input Overvoltage

8.3.5 Operating Voltage

The INA818 operates over a power-supply range of 4.5 V to 36 V (± 2.25 V to ± 18 V).

注意

Supply voltages higher than 40 V (± 20 V) can permanently damage the device. Parameters that vary over supply voltage or temperature are shown in *Typical Characteristics*.

8.3.6 Error Sources

Most modern signal-conditioning systems calibrate errors at room temperature. However, calibration of errors that result from a change in temperature is normally difficult and costly. Therefore, minimize these errors by choosing high-precision components, such as the INA818, that have improved specifications in critical areas that impact the precision of the overall system. 図 64 shows an example application.

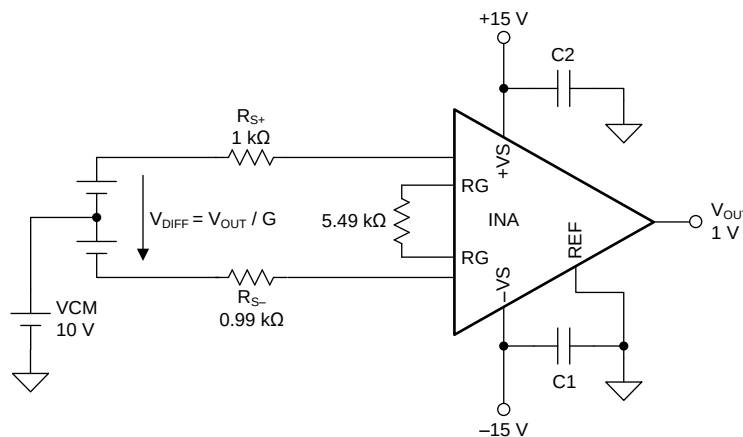


图 64. Example Application With $G = 10$ V/V and 1-V Output Voltage

Resistor-adjustable devices (such as the INA818) show the lowest gain error in $G = 1$ because of the inherently well-matched drift of the internal resistors of the differential amplifier. At gains greater than 1 (for instance, $G = 10$ V/V or $G = 100$ V/V), the gain error becomes a significant error source because of the contribution of the resistor drift of the 25-k Ω feedback resistors in conjunction with the external gain resistor. Except for very high gain applications, the gain drift is by far the largest error contributor compared to other drift errors, such as offset drift.

The INA818 offers excellent gain error over temperature for both $G > 1$ and $G = 1$ (no external gain resistor). 表 5 summarizes the major error sources in common INA applications and compares the three cases of $G = 1$ (no external resistor) and $G = 10$ (5.49-k Ω external resistor) and $G = 100$ (511- Ω external resistor). All calculations are assuming an output voltage of $V_{OUT} = 1$ V. Thus, the input signal V_{DIFF} (given by $V_{DIFF} = V_{OUT} / G$) exhibits smaller and smaller amplitudes with increasing gain G . $V_{DIFF} = 1$ mV at $G = 1000$ in this example. All calculations refer the error to the input for easy comparison and system evaluation. As 表 5 shows, errors generated by the input stage (such as input offset voltage) are more dominant at higher gain, while the effects of output stage are suppressed because they are divided by the gain when referring them back to the input. The gain error and gain drift error are much more significant for gains greater than 1 because of the contribution of the resistor drift of the 25-k Ω feedback resistors in conjunction with the external gain resistor. In most applications, static errors (absolute accuracy errors) can readily be removed during calibration in production, while the drift errors are the key factors limiting overall system performance.

表 4. System Specifications for Error Calculation

QUANTITY	VALUE	UNIT
V_{OUT}	1	V
VCM	10	V
VS	1	V
R_{S+}	1000	Ω
R_{S-}	999	Ω
RG tolerance	0.01	%
RG drift	10	ppm/°C
Temperature range upper limit	105	°C

表 5. Error Calculation

ERROR SOURCE	ERROR CALCULATION	INA818 VALUES				
		SPECIFICATION	UNIT	G = 1 ERROR (ppm)	G = 100 ERROR (ppm)	G = 1000 ERROR (ppm)
ABSOLUTE ACCURACY AT 25°C						
Input offset voltage	V _{OSI} / V _{DIFF}	35	µV	35	350	3500
Output offset voltage	V _{OSO} / (G × V _{DIFF})	300	µV	300	300	300
Input offset current	I _{OS} × maximum (R _{S+} , R _{S-}) / V _{DIFF}	0.5	nA	1	5	50
CMRR (min)	V _{CM} / (10 ^{CMRR/20} × V _{DIFF})	90 (G = 1), 110 (G = 10), 130 (G = 100)	dB	316	316	316
PSRR (min)	(V _{CC} -V _S)/ (10 ^{PSRR/20} × V _{DIFF})	110 (G = 1), 114 (G = 10), 130 (G = 100)	dB	3	20	32
Gain error from INA (max)	GE(%) × 10 ⁴	0.02 (G = 1), 0.15 (G = 10, 100)	%	200	1500	1500
Gain error from external resistor RG (max)	GE(%) × 10 ⁴	0.01	%	100	100	100
Total absolute accuracy error (ppm) at 25°C, worst case	sum of all errors	—	—	955	2591	5798
Total absolute accuracy error (ppm) at 25°C, average	rms sum of all errors	—	—	491	1604	3835
DRIFT TO 105°C						
Gain drift from INA (max)	GTC × (T _A – 25)	5 (G = 1), 35 (G = 10, 100)	ppm/°C	400	2800	2800
Gain drift from external resistor RG (max)	GTC × (T _A – 25)	10	ppm/°C	800	800	800
Input offset voltage drift (max)	(V _{OSI_TC} / V _{DIFF}) × (T _A – 25)	0.4	µV/°C	32	320	3200
Output offset voltage drift	[V _{OSO_TC} / (G × V _{DIFF})] × (T _A – 25)	5	µV/°C	400	400	400
Offset current drift	I _{OS_TC} × maximum (R _{S+} , R _{S-}) × (T _A – 25) / V _{DIFF}	20	pA/°C	2	16	160
Total drift error to 105°C (ppm), worst case	sum of all errors	—	—	1634	4336	7360
Total drift error to 105°C (ppm), typical	rms sum of all errors	—	—	980	2957	4348
RESOLUTION						
Gain nonlinearity		10 (G = 1, 10), 15 (G = 100)	ppm of FS	10	10	15
Voltage noise (at 1 kHz)	$\sqrt{BW} \times \sqrt{(e_{NI})^2 + \left(\frac{e_{NO}}{G}\right)^2} \times \frac{6}{V_{DIFF}}$	e _{NI} = 8, e _{NO} = 90	µV _{PP}	1204	1070	3941
Current noise (at 1kHz)	I _N × maximum (R _{S+} , R _{S-}) × √BW / V _{DIFF}	0.13	pA/√Hz	0.3	2	11
Total resolution error (ppm), worst case	sum of all errors	—	—	1214	1080	3956
Total resolution error (ppm), typical	rms sum of all errors	—	—	1204	1070	3941
TOTAL ERROR						
Total error (ppm), worst case	sum of all errors	—	—	3802	8007	17113
Total error (ppm), typical	rms sum of all errors	—	—	1628	3530	7010

8.4 Device Functional Modes

The INA818 has a single functional mode and operates when the power-supply voltage is greater than 4.5 V (± 2.25 V). The maximum power-supply voltage for the INA818 is 36 V (± 18 V.)

9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

9.1.1 Reference Pin

The output voltage of the INA818 is developed with respect to the voltage on the reference pin, REF. In dual-supply operation, REF (pin 6) is connected to the low-impedance system ground. In single-supply operation, offsetting the output signal to a precise midsupply level is useful (for example, 2.5 V in a 5-V supply environment). To accomplish this level shift, a voltage source must be connected to the REF pin to level-shift the output so that the INA818 drives a single-supply ADC.

The voltage source applied to the reference pin must have a low output impedance. As shown in [Figure 65](#), any resistance at the reference pin (shown as R_{REF} in [Figure 65](#)) is in series with an internal 40-k Ω resistor.

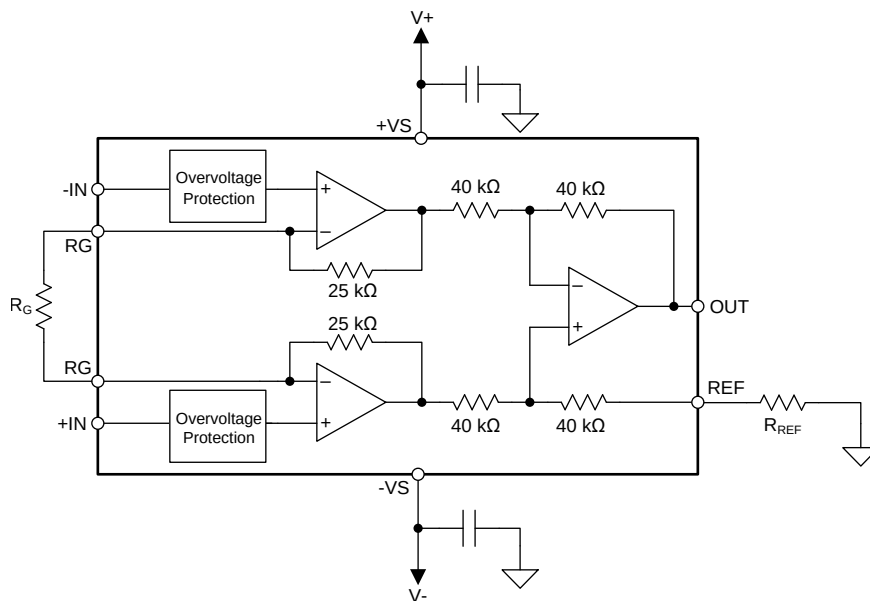


Figure 65. Parasitic Resistance Shown at the Reference Pin

Application Information (continued)

The parasitic resistance at the reference pin (R_{REF}) creates an imbalance in the four resistors of the internal difference amplifier, which degrades the common-mode rejection ratio (CMRR). Figure 66 shows the degradation in CMRR of the INA818 as a result of increased resistance at the reference pin. For the best performance, keep the source impedance to the REF pin (R_{REF}) below 5 Ω .

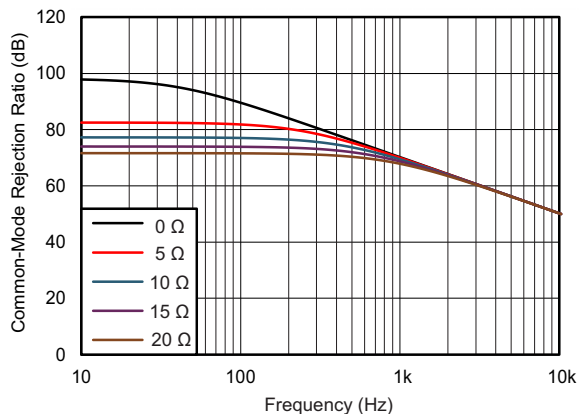


Figure 66. The Effect of Increasing Resistance at the Reference Pin

Voltage-reference devices are a suitable option for providing a low-impedance voltage source for the reference pin. However, if a resistor voltage divider generates a reference voltage, the divider must be buffered by an op amp, as Figure 67 shows, in order to avoid CMRR degradation.

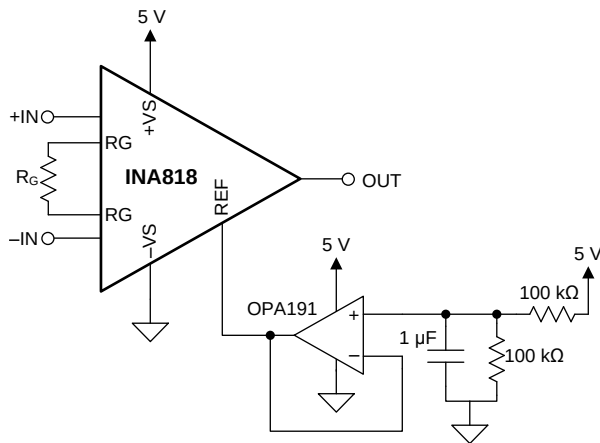


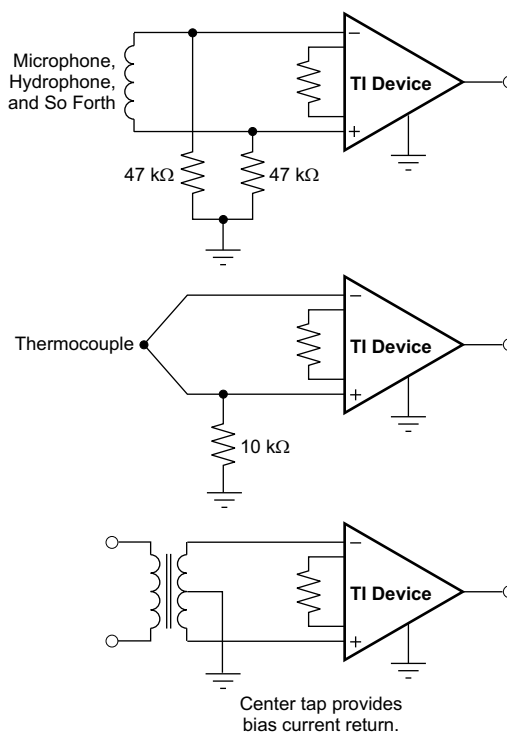
Figure 67. Using an Op Amp to Buffer Reference Voltages

Application Information (continued)

9.1.2 Input Bias Current Return Path

The input impedance of the INA818 is extremely high—approximately 100 G Ω . However, a path must be provided for the input bias current of both inputs. This input bias current is typically 150 pA. High input impedance means that this input bias current changes very little with varying input voltage.

For proper operation, input circuitry must provide a path for input bias current. [Figure 68](#) shows various provisions for an input bias current path. Without a bias current path, the inputs float to a potential that exceeds the common-mode range of the INA818, and the input amplifiers saturate. If the differential source resistance is low, the bias current return path can connect to one input (as shown in the thermocouple example in [Figure 68](#)). With a higher source impedance, using two equal resistors provides a balanced input with possible advantages of a lower input offset voltage as a result of bias current and better high-frequency common-mode rejection.



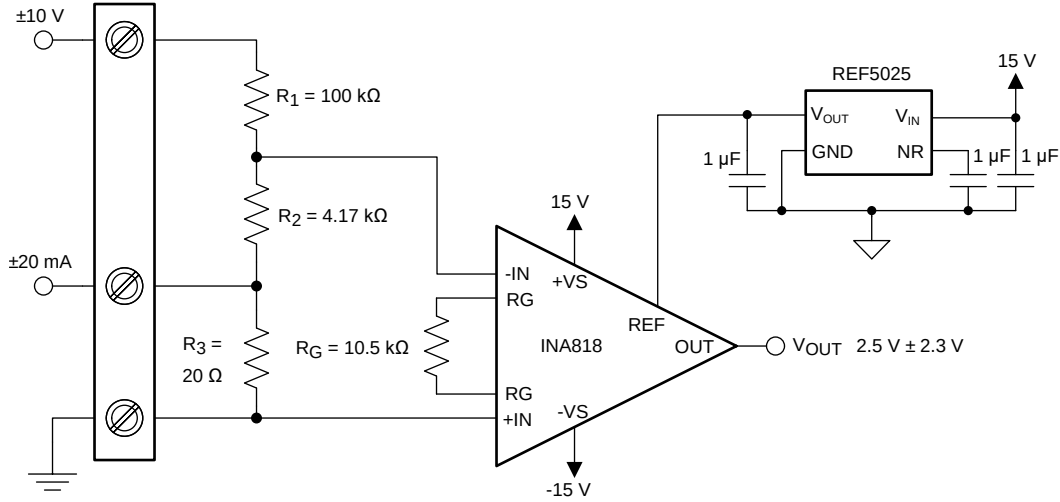
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Figure 68. Providing an Input Common-Mode Current Path

9.2 Typical Applications

9.2.1 Three-Pin Programmable Logic Controller (PLC)

Figure 69 shows a three-pin programmable-logic controller (PLC) design for the INA818. This PLC reference design accepts inputs of ± 10 V or ± 20 mA. The output is a single-ended voltage of 2.5 V ± 2.3 V (or 200 mV to 4.8 V). Many PLCs typically have these input and output ranges.



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Figure 69. PLC Input (± 10 V, 4 mA to 20 mA)

9.2.1.1 Design Requirements

For this application, the design requirements are as follows:

- 4-mA to 20-mA input with less than $20\text{-}\Omega$ burden
- ± 20 -mA input with less than $20\text{-}\Omega$ burden
- ± 10 -V input with impedance of approximately $100\text{ k}\Omega$
- Maximum 4-mA to 20-mA or ± 20 -mA burden voltage equal to ± 0.4 V
- Output range within 0 V to 5 V

9.2.1.2 Detailed Design Procedure

There are two modes of operation for the circuit shown in Figure 69: current input and voltage input. This design requires $R_1 \gg R_2 \gg R_3$. Given this relationship, Equation 3 calculates the current input mode transfer function.

$$V_{\text{OUT-I}} = V_D \times G + V_{\text{REF}} = -(I_{\text{IN}} \times R_3) \times G + V_{\text{REF}}$$

where

- G represents the gain of the instrumentation amplifier
- V_D represents the differential voltage at the INA818 inputs
- V_{REF} is the voltage at the INA818 REF pin
- I_{IN} is the input current

(3)

Equation 4 shows the transfer function for the voltage input mode.

$$V_{\text{OUT-V}} = V_D \times G + V_{\text{REF}} = -\left[V_{\text{IN}} \times \frac{R_2}{R_1 + R_2}\right] \times G + V_{\text{REF}}$$

where

- V_{IN} is the input voltage

(4)

Typical Applications (continued)

R_1 sets the input impedance of the voltage input mode. The minimum typical input impedance is 100 k Ω . 100 k Ω is selected for R_1 because increasing the R_1 value also increases noise. The value of R_3 must be extremely small compared to R_1 and R_2 . 20 Ω for R_3 is selected because that resistance value is much smaller than R_1 and yields an input voltage of ± 400 mV when operated in current mode (± 20 mA).

Use 式 5 to calculate R_2 given $V_D = \pm 400$ mV, $V_{IN} = \pm 10$ V, and $R_1 = 100$ k Ω .

$$V_D = V_{IN} \times \frac{R_2}{R_1 + R_2} \rightarrow R_2 = \frac{R_1 \times V_D}{V_{IN} - V_D} = 4.167 \text{ k}\Omega \quad (5)$$

The value obtained from 式 5 is not a standard 0.1% value, so 4.17 k Ω is selected. R_1 and R_2 also use 0.1% tolerance resistors to minimize error.

Use 式 6 to calculate the ideal gain of the instrumentation amplifier.

$$G = \frac{V_{OUT} - V_{REF}}{V_D} = \frac{4.8 \text{ V} - 2.5 \text{ V}}{400 \text{ mV}} = 5.75 \frac{\text{V}}{\text{V}} \quad (6)$$

式 7 calculates the gain-setting resistor value using the INA818 gain equation, 式 1.

$$R_G = \frac{50 \text{ k}\Omega}{G - 1} = \frac{50 \text{ k}\Omega}{5.75 - 1} = 10.5 \text{ k}\Omega \quad (7)$$

10.5 k Ω is a standard 0.1% resistor value that can be used in this design.

9.2.1.3 Application Curves

图 70 and 图 71 show typical characteristic curves for the circuit in 图 69.

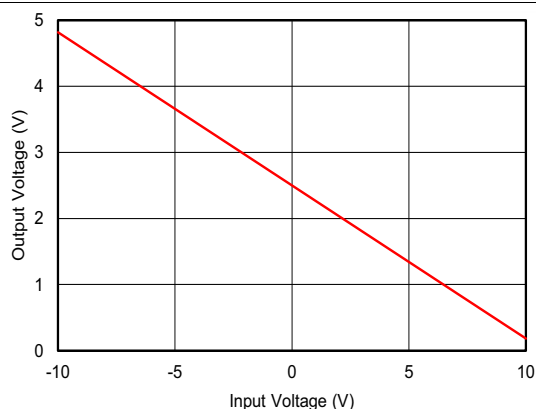


图 70. PLC Output Voltage vs Input Voltage

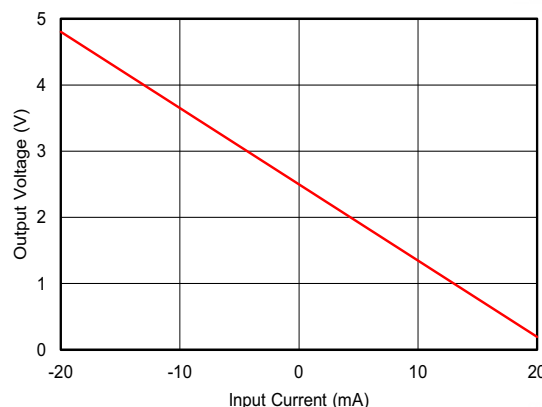
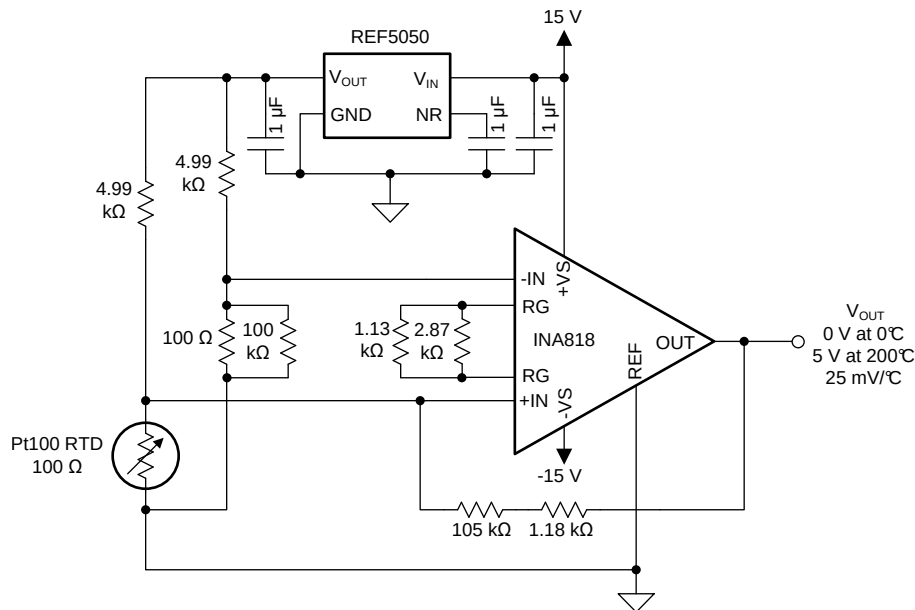


图 71. PLC Output Voltage vs Input Current

Typical Applications (continued)

9.2.2 Resistance Temperature Detector Interface

Figure 72 illustrates a 3-wire interface circuit for resistance temperature detectors (RTDs). The circuit incorporates analog linearization and has an output voltage range from 0 V to 5 V. The linearization technique employed is described in the [Analog linearization of resistance temperature detectors analog application journal](#). Series and parallel combinations of standard 1% resistor values are used to achieve less than 0.02°C of error over a 200°C temperature span.



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Figure 72. A 3-Wire Interface for RTDs With Analog Linearization

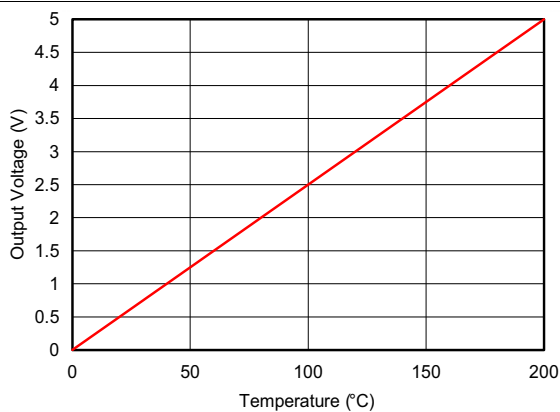


Figure 73. Transfer Function of a 3-Wire RTD Interface

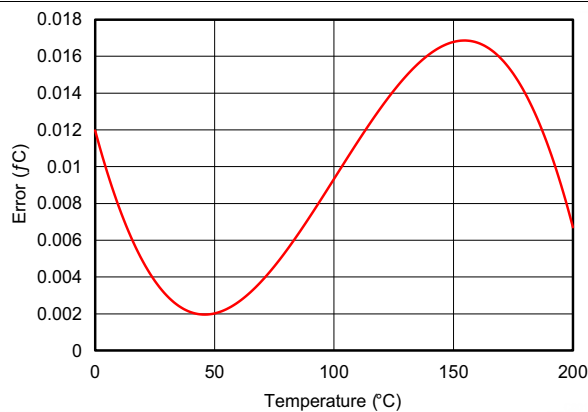


Figure 74. Temperature Error Over the Full Temperature Range

10 Power Supply Recommendations

The nominal performance of the INA818 is specified with a supply voltage of ± 15 V and midsupply reference voltage. The device can also be operated using power supplies from ± 2.25 V (4.5 V) to ± 18 V (36 V) and non-midsupply reference voltages with excellent performance. Parameters that can vary significantly with operating voltage and reference voltage are shown in the [Typical Characteristics](#) section.

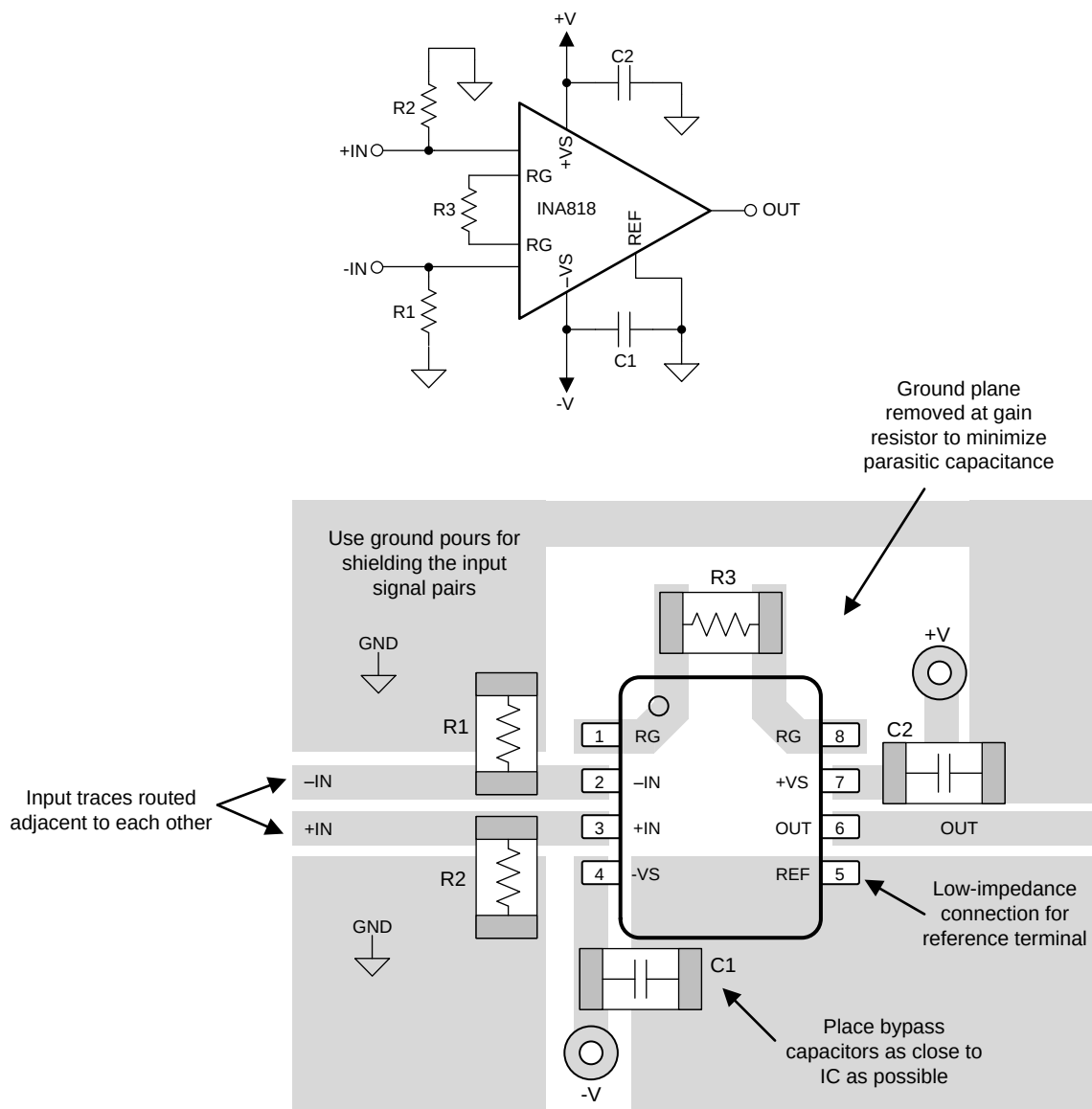
11 Layout

11.1 Layout Guidelines

Attention to good layout practices is always recommended. For best operational performance of the device, use good PCB layout practices, including:

- Take care to make sure that both input paths are well-matched for source impedance and capacitance to avoid converting common-mode signals into differential signals. Even slight mismatch in parasitic capacitance at the gain setting pins can degrade CMRR over frequency. For example, in applications that implement gain switching using switches or PhotoMOS[®] relays to change the value of R_G , select the component so that the switch capacitance is as small as possible and most importantly so that capacitance mismatch between the R_G pins is minimized.
- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and of the device itself. Bypass capacitors reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1- μ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from $V+$ to ground is applicable for single-supply applications.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better than in parallel with the noisy trace.
- Place the external components as close to the device as possible. As shown in [Figure 75](#), keeping R_G close to the pins minimizes parasitic capacitance.
- Keep the traces as short as possible.

11.2 Layout Example



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75. Example Schematic and Associated PCB Layout

12 デバイスおよびドキュメントのサポート

12.1 ドキュメントのサポート

12.1.1 関連資料

関連資料については、以下を参照してください。

- テキサス・インスツルメンツ、『[Universal Instrumentation Amplifier EVM](#)』ユーザー・ガイド (英語)
- テキサス・インスツルメンツ、『[Comprehensive Error Calculation for Instrumentation Amplifiers](#)』アプリケーション・ノート (英語)

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Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

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12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 メカニカル、パッケージ、および注文情報

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
INA818ID	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA818
INA818ID.B	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA818
INA818IDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA818
INA818IDR.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA818
INA818IDRG4.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA818

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

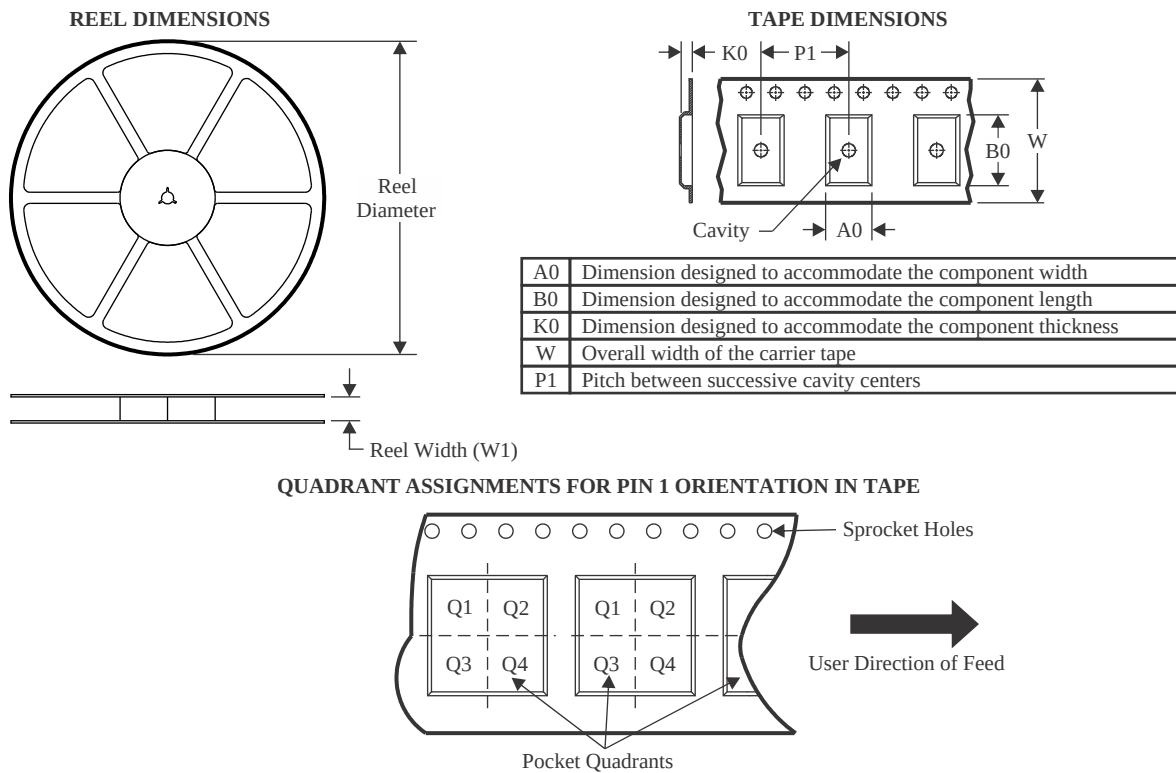
⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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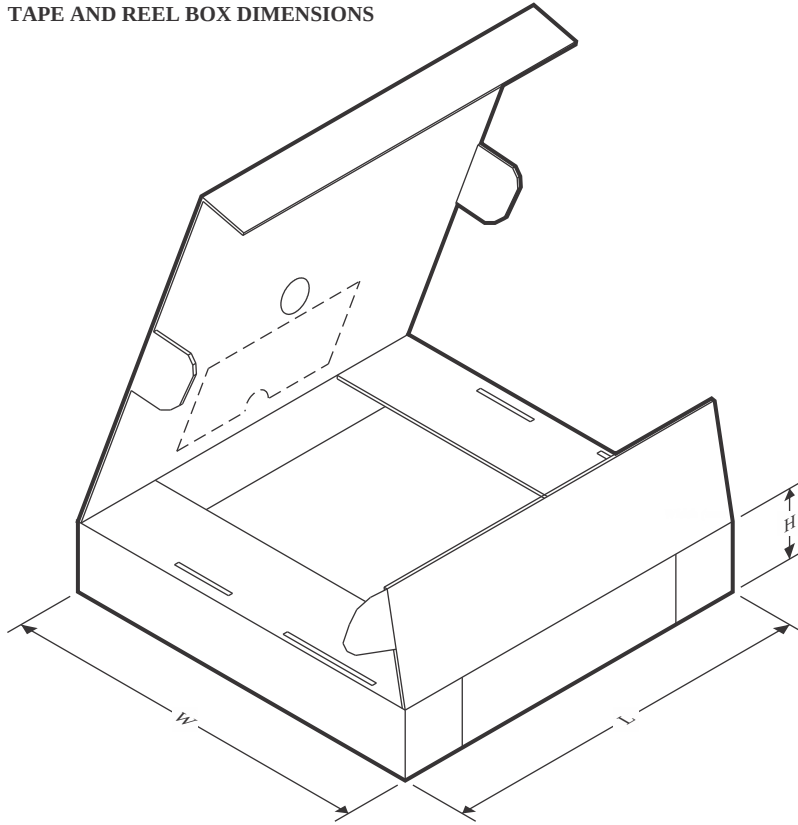
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA818IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

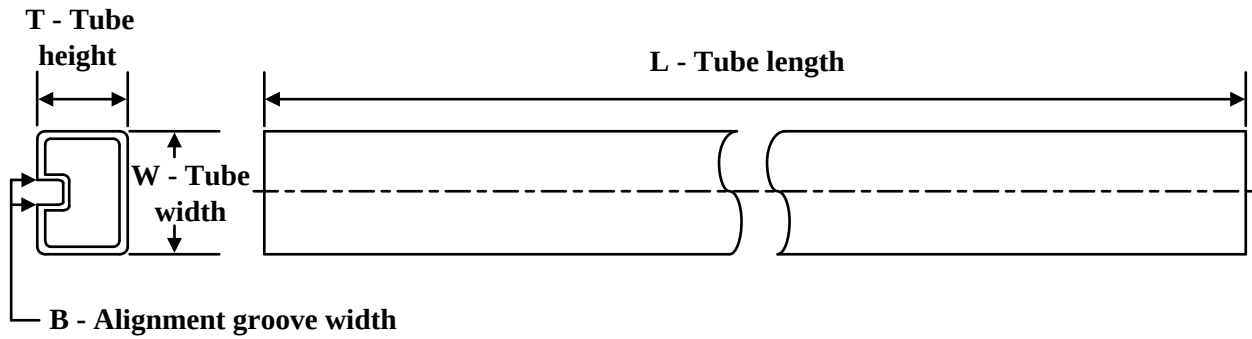
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA818IDR	SOIC	D	8	2500	356.0	356.0	35.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
INA818ID	D	SOIC	8	75	506.6	8	3940	4.32
INA818ID.B	D	SOIC	8	75	506.6	8	3940	4.32



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

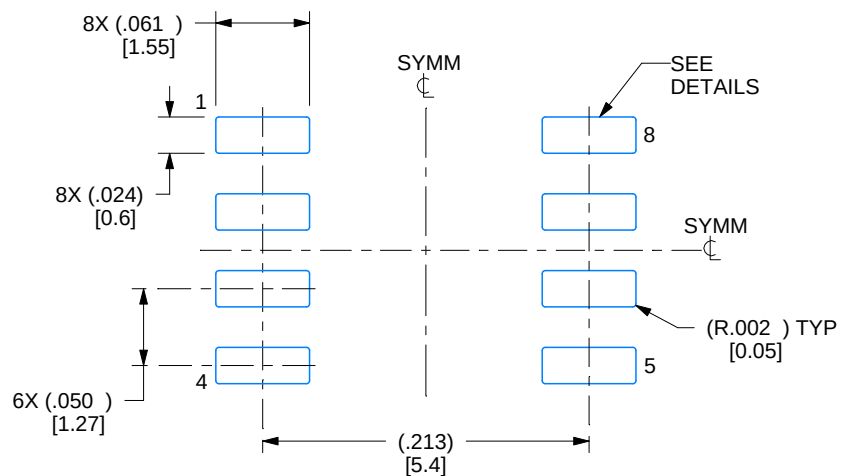


1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

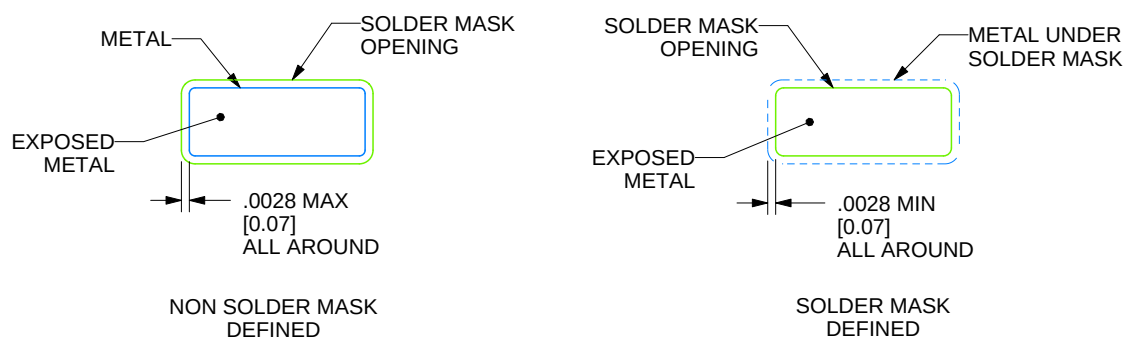
D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

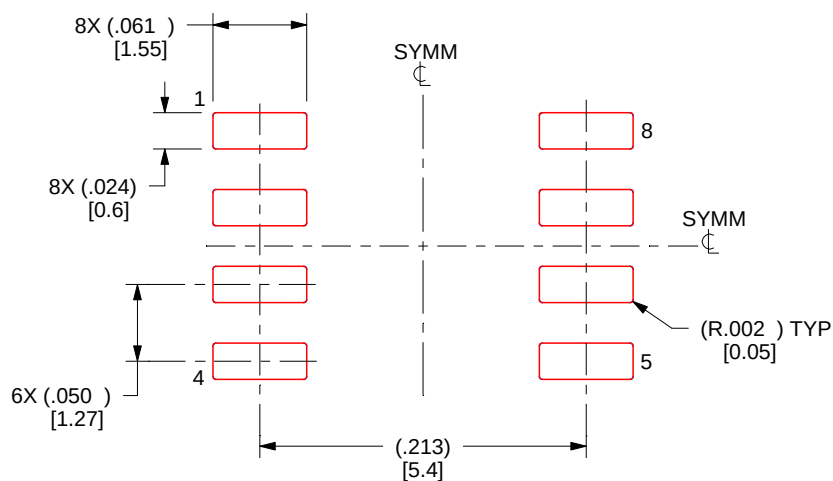
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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